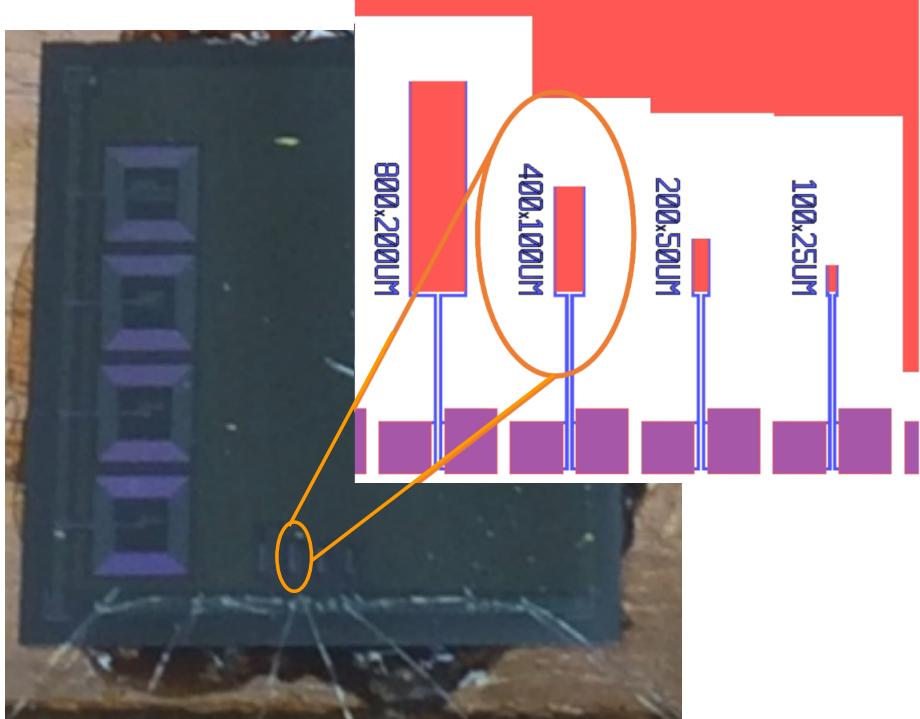
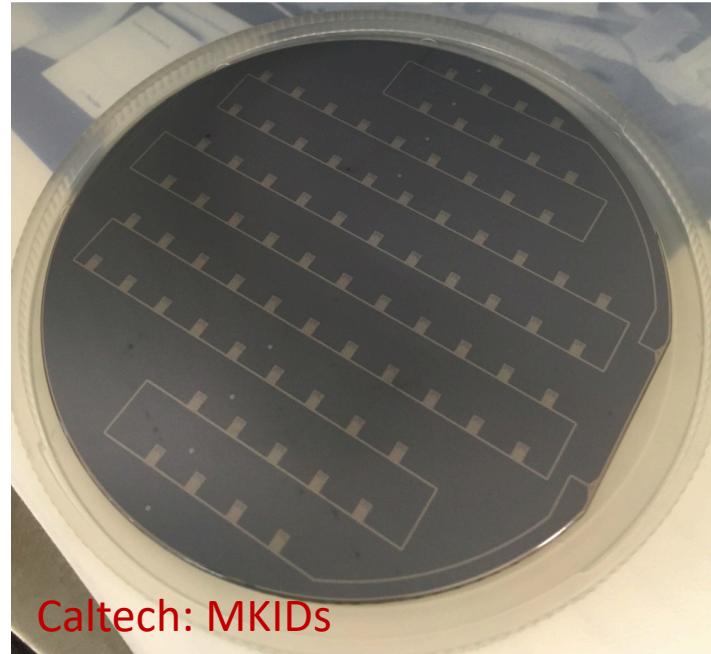


NTD, TES, MKID and SNSPD Sensors in Dark Matter



Matt Pyle
UC Berkeley
New Directions Fermilab
June 4 2019

Outline

- Light Mass Dark Matter Design Drivers
- TES
 - Athermal phonon collection and concentration schemes
- NTDs
- MKIDs
- SNSPDs
 - Energy Reconstruction
- Proposed/Running Experiments

Light Mass Dark Matter Direct Detection Design Drivers

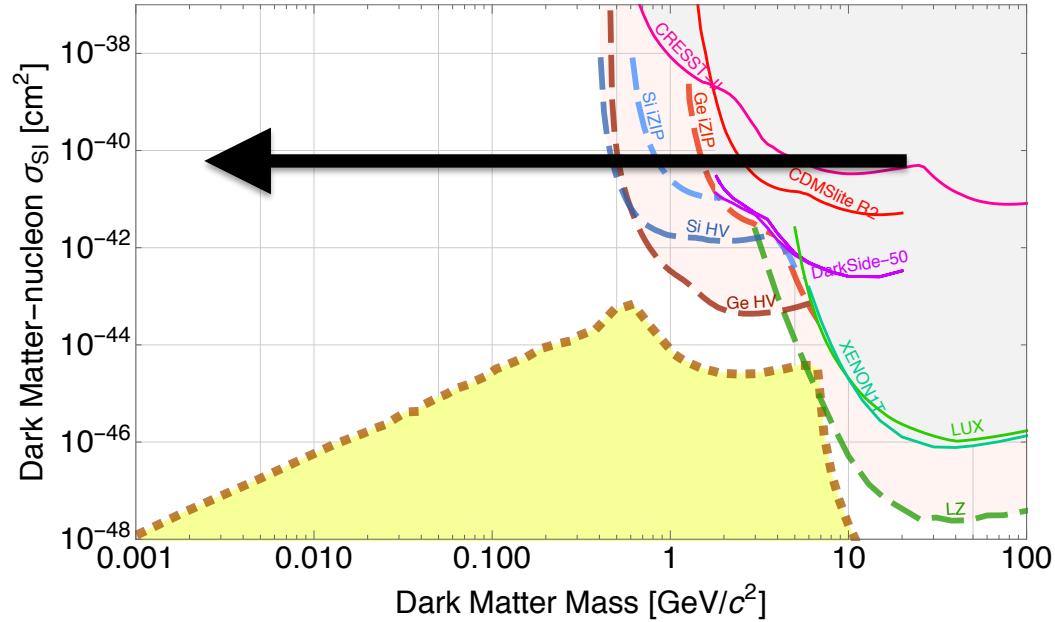
Light Mass DM Design Drivers:

Exposure

$$R = \sigma n_{DM} v_{DM} N_{exp}$$

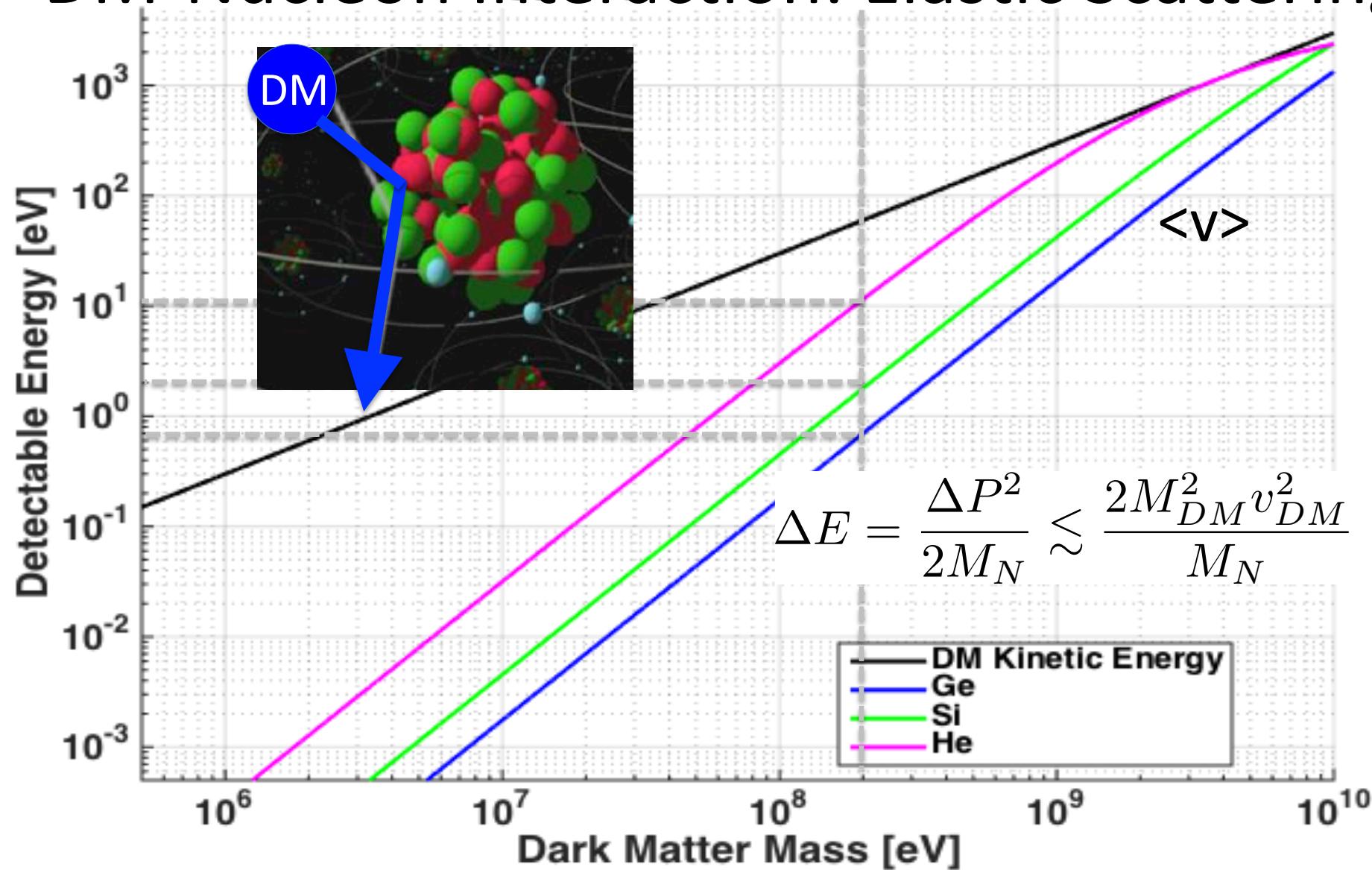
$$= \sigma \frac{\rho_{DM}}{M_{DM}} v_{esc} N_{exp}$$

Interaction
Rate scales
with $1/M_{DM}$



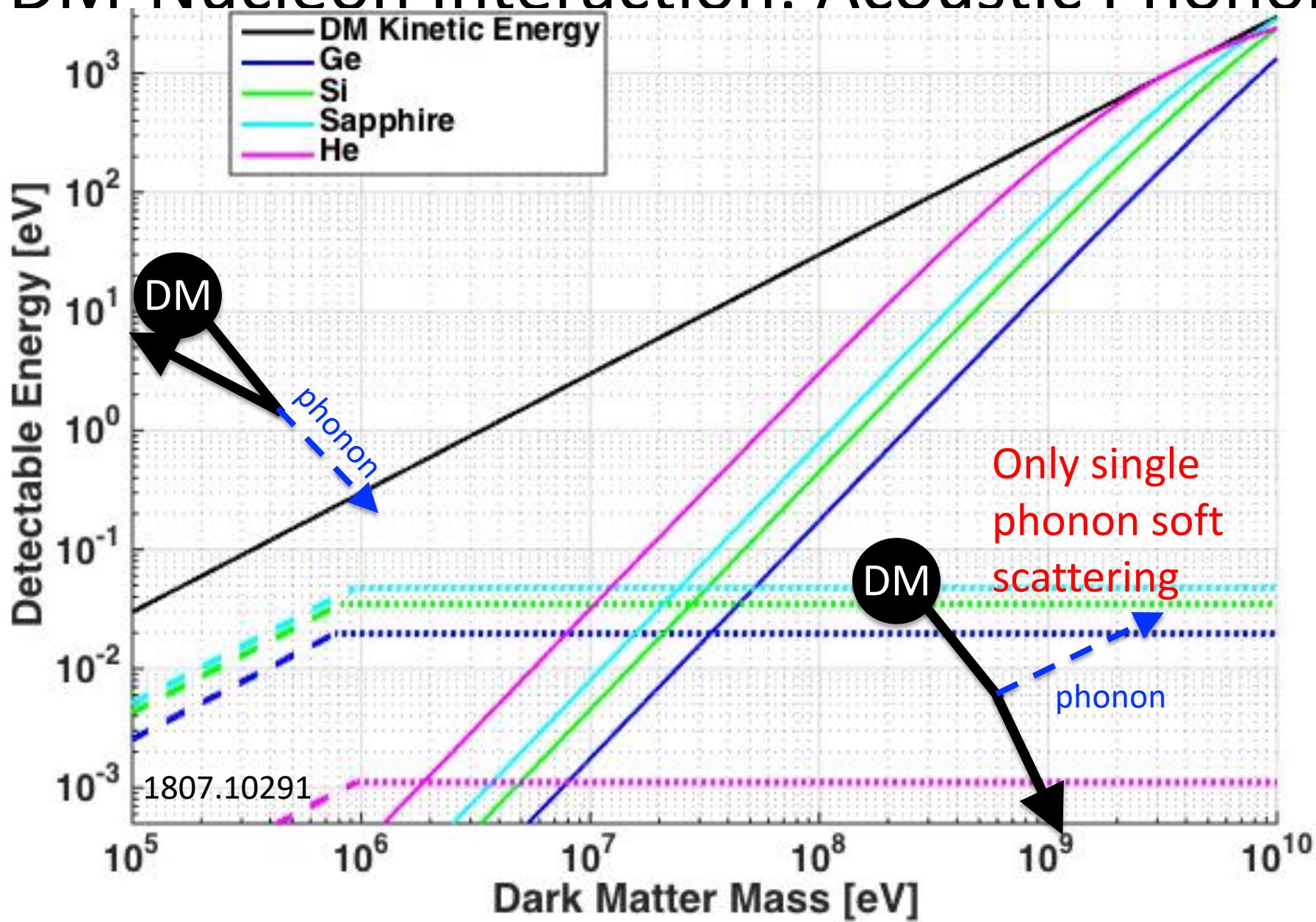
LZ needs 10 tons to get to 10^{-47} cm 2 at 100GeV, Light Mass DM searches only needs 10kg to reach the same level at 100MeV.

DM-Nucleon Interaction: Elastic Scattering



Primary Design Driver: Vibrational Energy Sensitivity

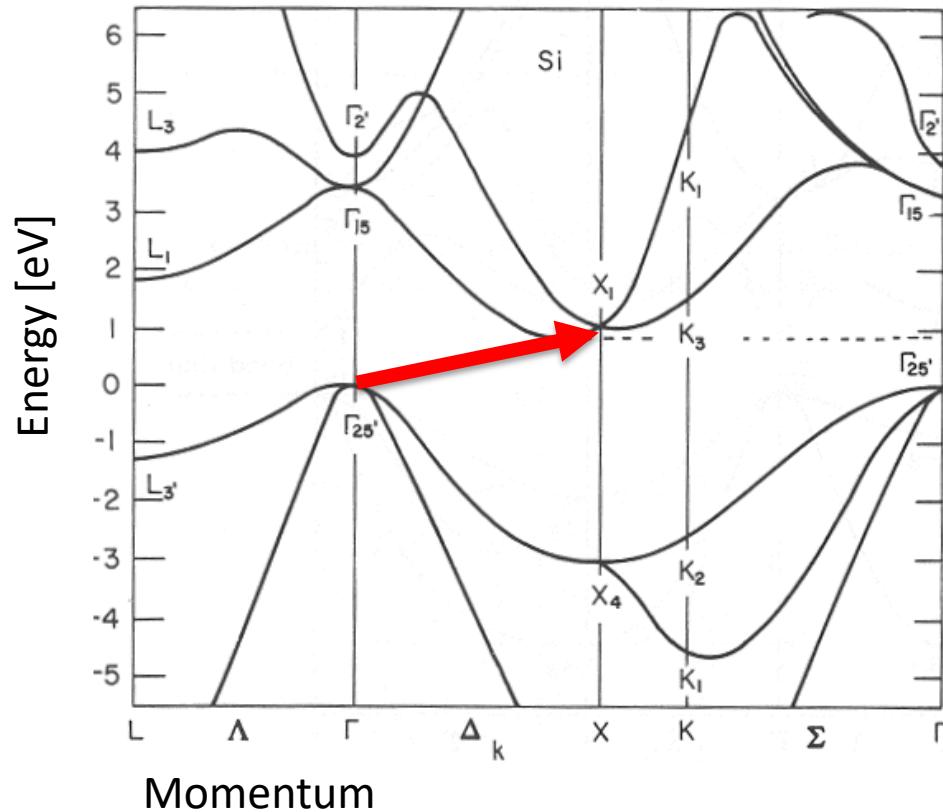
DM-Nucleon Interaction: Acoustic Phonon



Primary design driver: Still Vibrational Energy Sensitivity

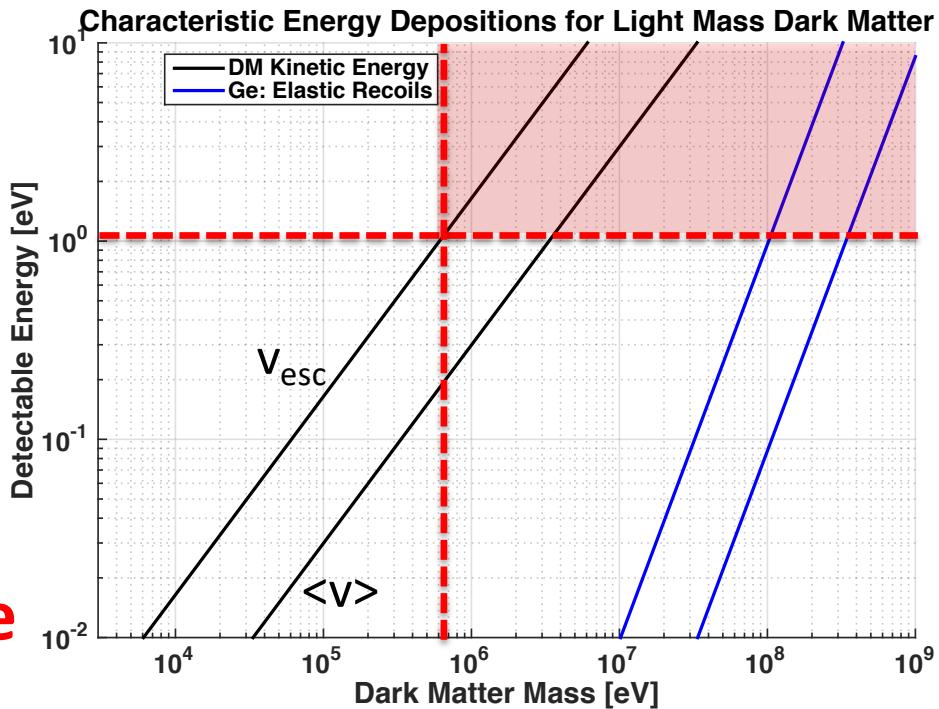
DM-Electronic Interactions: Inelastic e⁻ recoil

E [eV] Band Diagram for Si

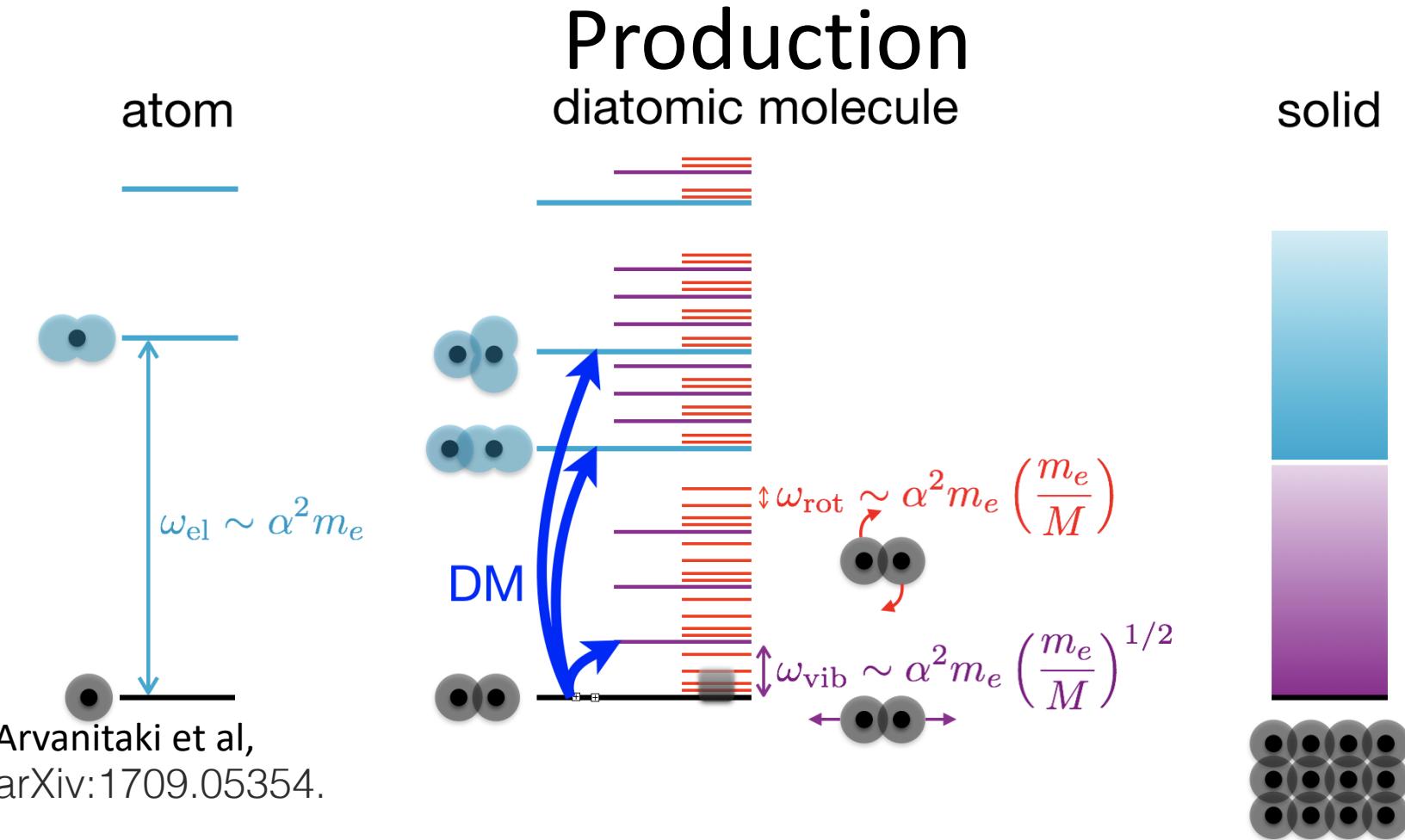


Design Driver: Sensitivity to single e/h pairs (eV energy) with negligible dark count rate

- e⁻ excitation momentum and energy scales in semiconductors well matched to 1 MeV-100MeV DM
- Essig et al: 1108.5383



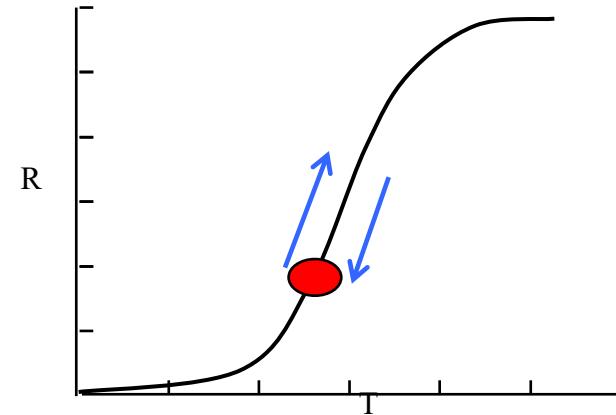
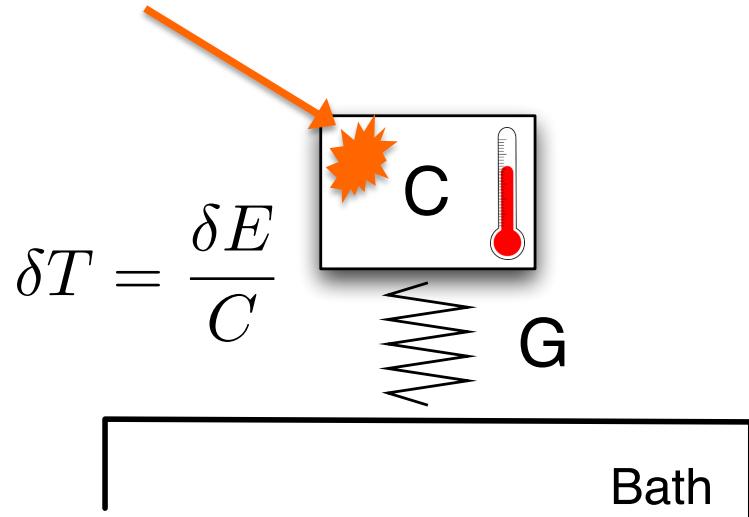
DM-Molecular/Atom Absorption: Photon



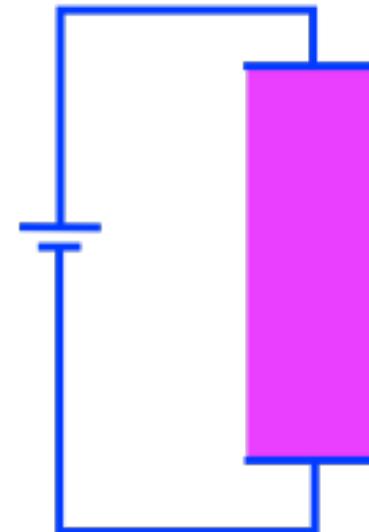
**Design Driver: 100meV –eV scale
single photon sensitivity**

Transition Edge Sensor

The Simplest Thermal Calorimeter

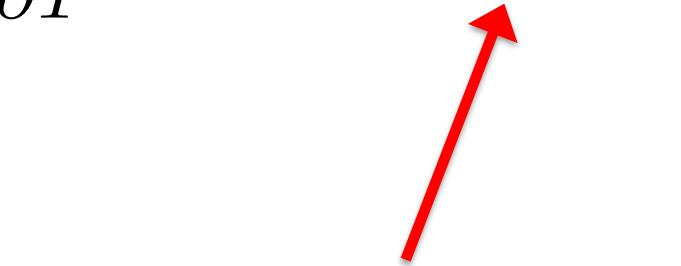
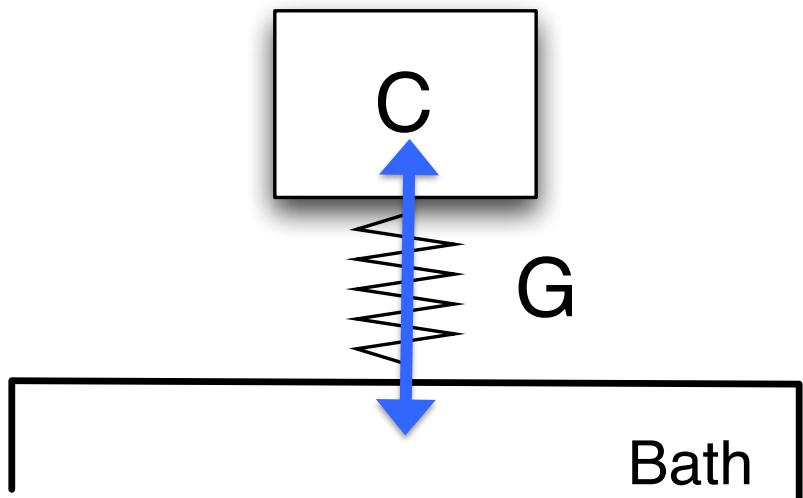


Transition Edge Sensor (TES): A superconducting metal film (W) that is externally biased so as to be within its superconducting/normal transition



TES Sensitivity

$$\begin{aligned}\sigma_{\langle E \rangle}^2 &= \sum_i (E_i - \langle E \rangle)^2 \frac{e^{-\beta E_i}}{\sum_j e^{-\beta E_j}} \\ &= \frac{\sum_i E_i^2 e^{-\beta E_i}}{\sum_j e^{-\beta E_j}} - \langle E \rangle^2 \\ &= -\frac{\partial \langle E \rangle}{\partial \beta} = \frac{\partial \langle E \rangle}{\partial T} k_b T^2 = C k_b T^2\end{aligned}$$

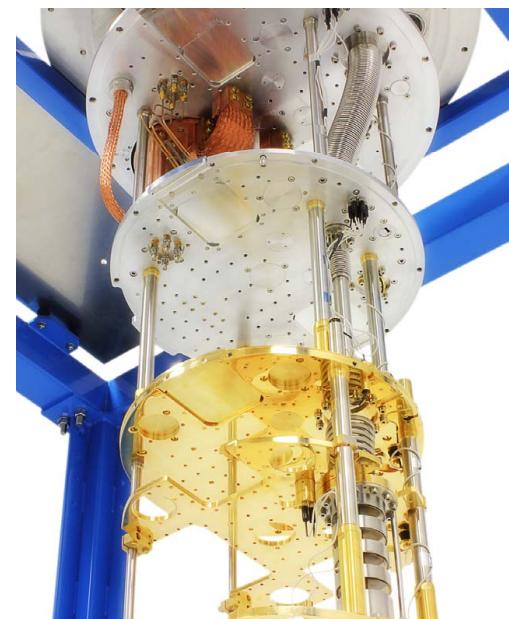


~ Intrinsic Thermal Noise
of Calorimeters

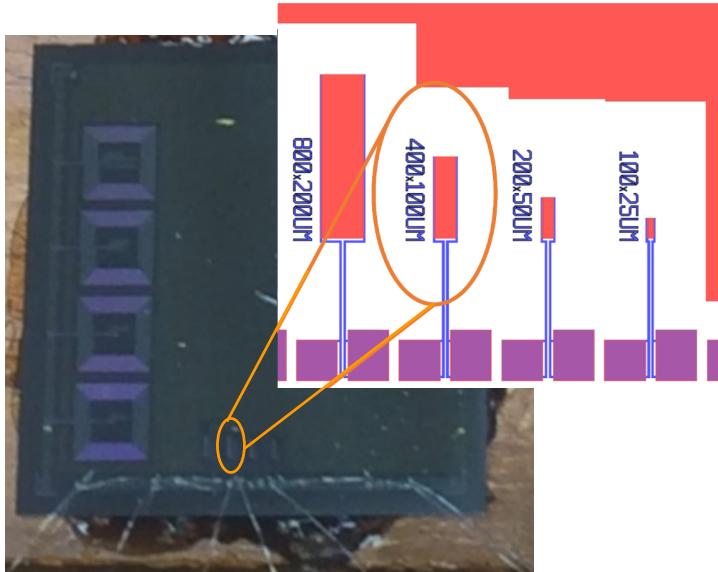
TES Scaling Laws & Optimization

$$\sigma_{\langle E \rangle}^2 = C k_b T_c^2 \propto V T_c^3$$

- Minimize Temperature
 - Dilution Refrigerators can cool detectors to 5mK
 - $T_c \rightarrow 1.5 \times T_{\text{bath}}$
- Minimize Volume



100meV Threshold TES are really small!



$$\sigma_{\text{theory}} \sim 20\text{meV}$$

$$T_c = 41\text{mK}$$

$$V = 400\text{um} \times 100\text{um} \times 40\text{nm}$$

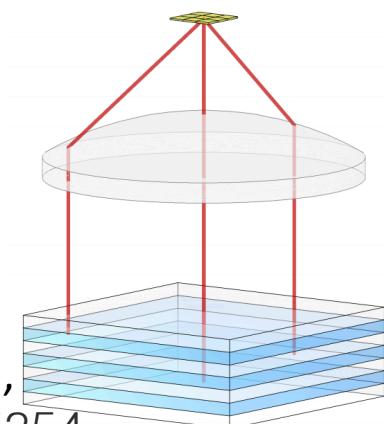
$$= 1.6 \times 10^{-9} \text{ cm}^3$$

$$= 30\text{ng}$$

1 gram of active target mass -> 30M channels

1 cm² of active area -> 2500 channels

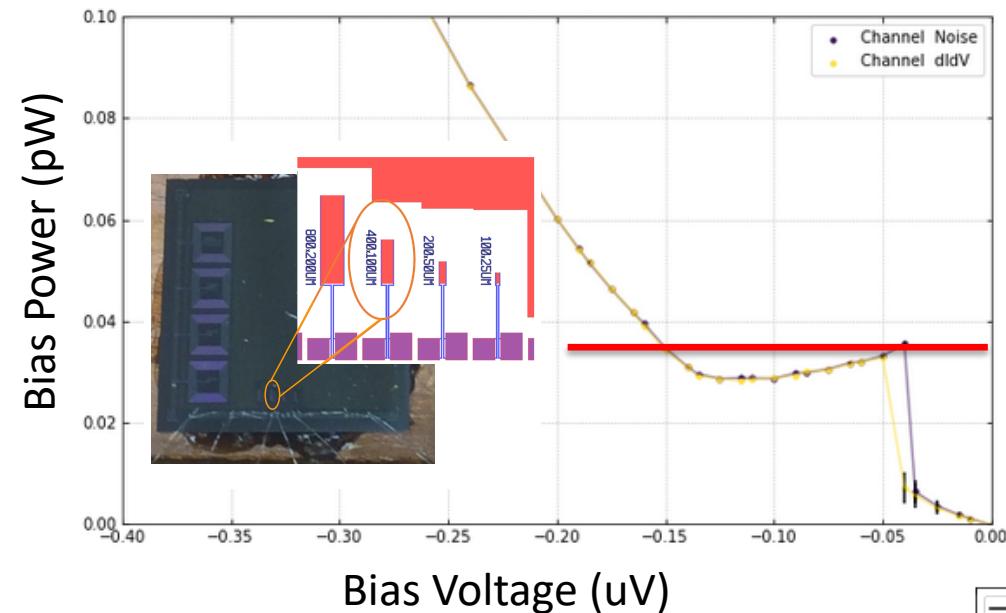
TES can only be used by themselves when photon collecting over a very small area



Arvanitaki et al,
arXiv:1709.05354.

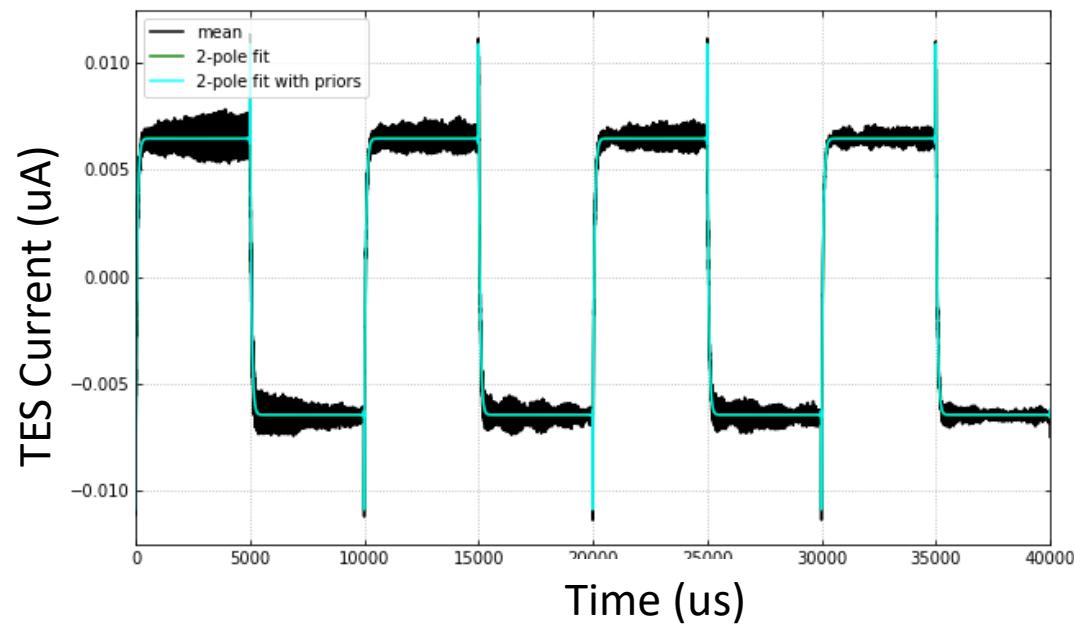
Currently Achieved TES Energy Sensitivity: $100\mu\text{m} \times 400\mu\text{m} \times 40\text{nm}$

TES Power vs TES Bias Voltage



- T. Aramaki, P. Brink, C. Fink, R. Harris, Y. Kolomensky, R. Mahapatra, N. Mirabolfathi, R. Partridge, M. Platt, MP, B. Sadoulet, B. Serfass, S. Watkins
- $100\mu\text{m} \times 400\mu\text{m} \times 40\text{nm}$ W TES
- $T_c = 41\text{mK}$
- Normal Resistance: $630\text{m}\Omega$
- Bias Power: 35fW

TES Response to Square Wave Jitter

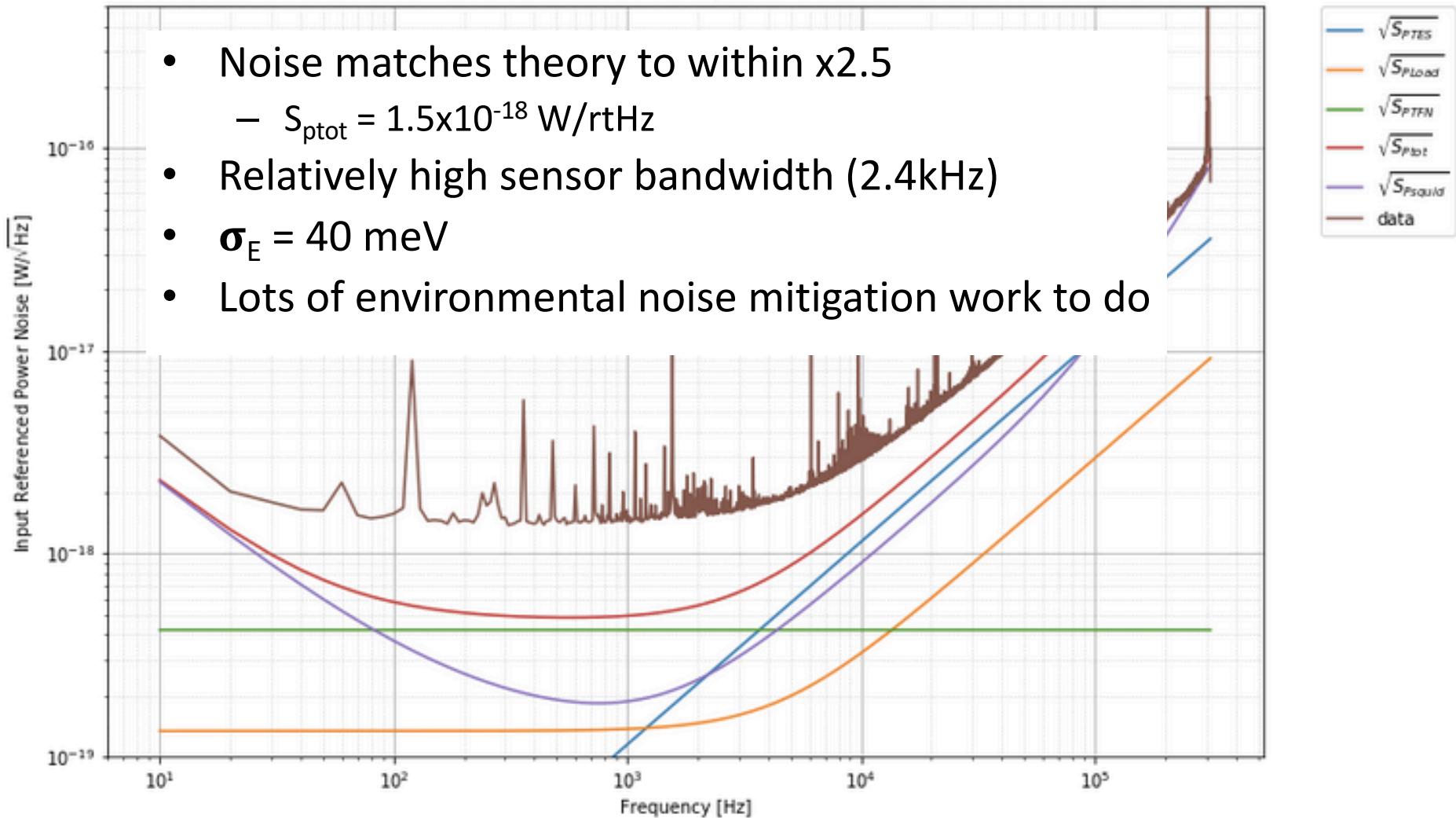


- Complex Impedance
 - Simple 2 pole TES dynamical model perfectly fits response
- TES falltime: $\sim 66\text{us}$ (2.4kHz)
 - Relatively fast
 - Long term $\rightarrow 1\text{ms}$ and allow athermal phonons to ballistically bounce

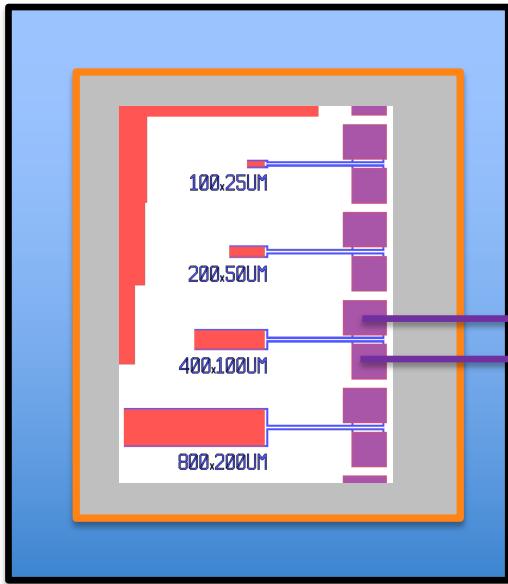
100um x400um TES Noise

Power Noise For $R_0 : 47.85 \text{ m}\Omega$

- Noise matches theory to within x2.5
 - $S_{\text{ptot}} = 1.5 \times 10^{-18} \text{ W/rtHz}$
- Relatively high sensor bandwidth (2.4kHz)
- $\sigma_E = 40 \text{ meV}$
- Lots of environmental noise mitigation work to do

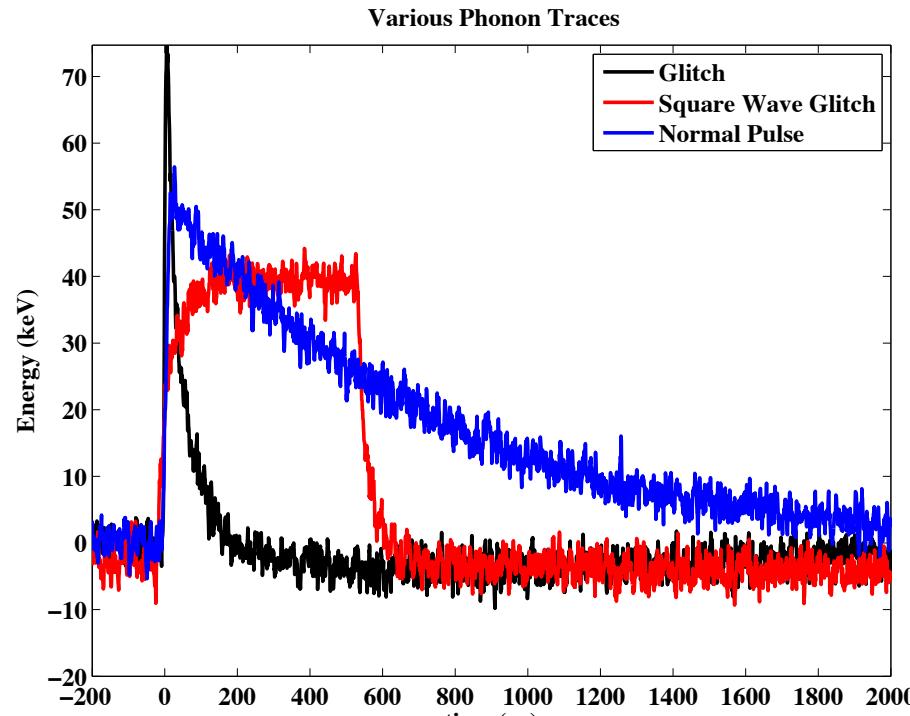


TES: Environmental Noise Susceptibility



- TES is a resistor ... you can heat a resistor with an E&M wave of any frequency
- 5fW of DC Environmental EMI coming down the TES bias lines
- Lots of AC power glitches seen too

Big Challenge: Need to continue to improve Environmental Isolation

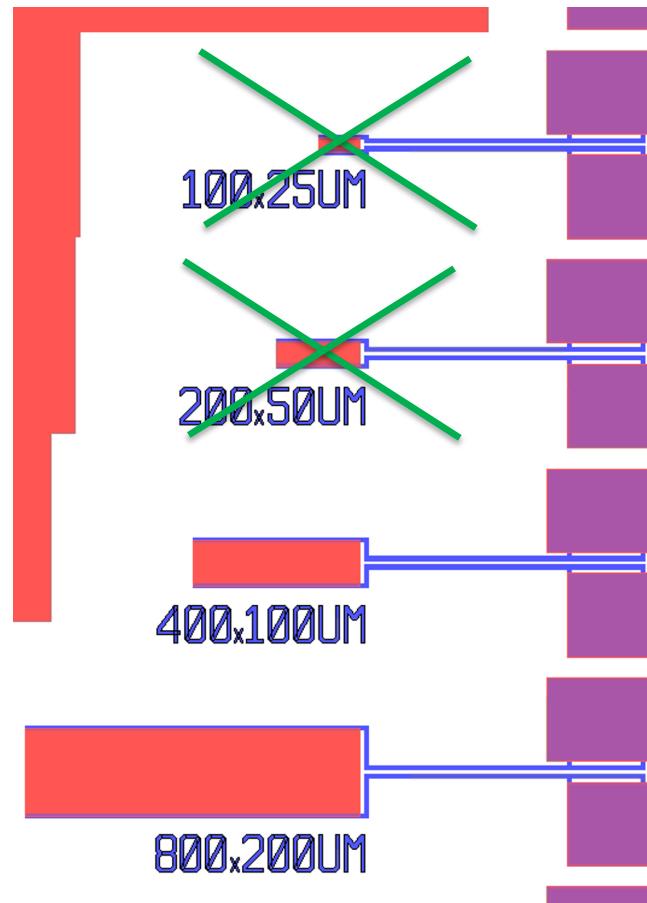


TES R&D

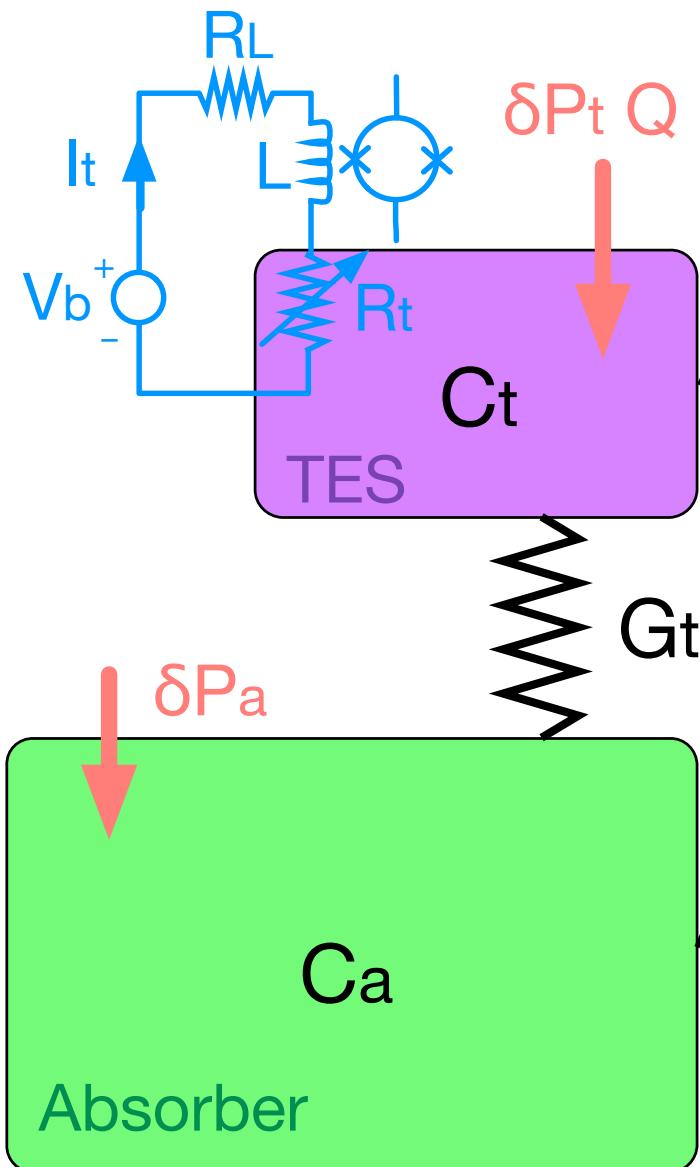
Energy Sensitivity: 40meV \rightarrow 1meV

R&D Work Plan

- Lower T_c from 40mK \rightarrow 10mK.
 - x8 sensitivity improvement
- Lower volume by x16
 - x4 sensitivity improvement
- Decrease environmental noise by 50dB ... there is a reason I'm not showing the performance of the 200umx50um TES

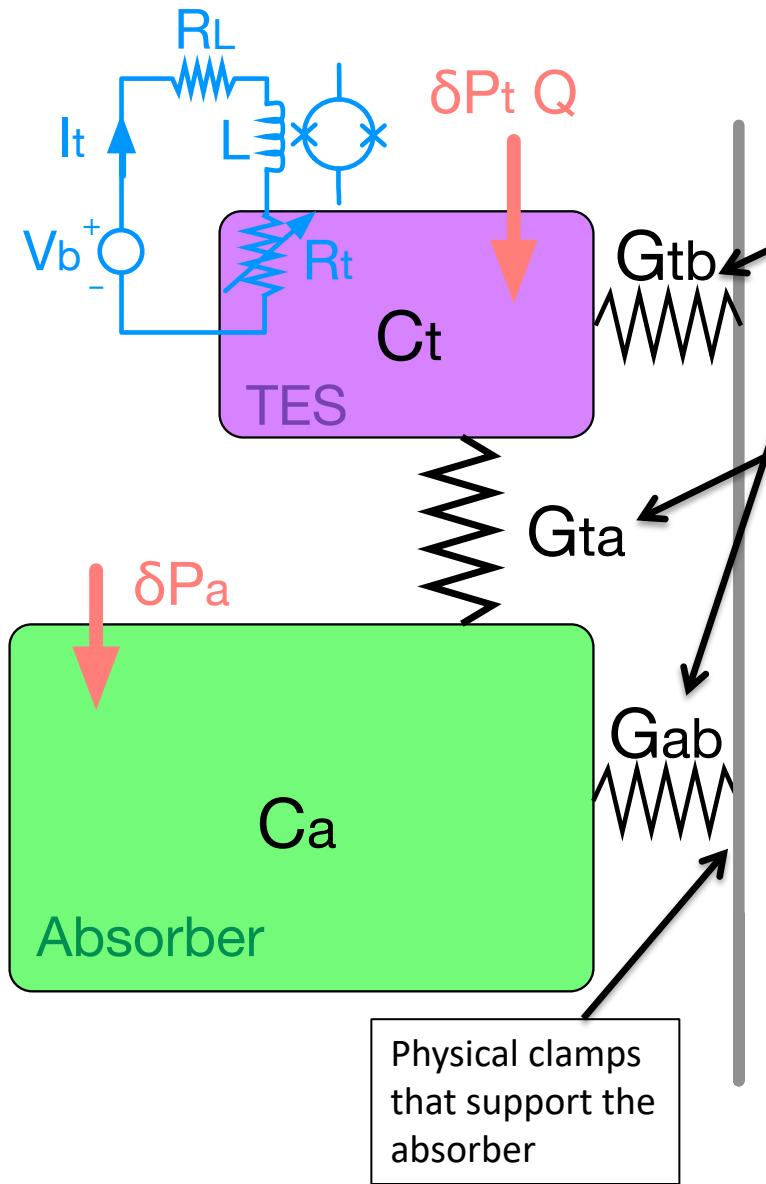


Increase Target Volume: Add Insulating Absorber



- Couple the sensor to a large volume insulator \rightarrow low heat capacity.
- Vibrational Energy in the Absorber is transported through G_t to the electronic system of the TES

Problem: Decoupling between the Sensor and Absorber



- Kapitza boundary conductance scale as T^3
- e-/phonon thermal conductance scales as T^4

As T is decreased, it's harder and harder to keep the sensor thermally coupled to the absorber

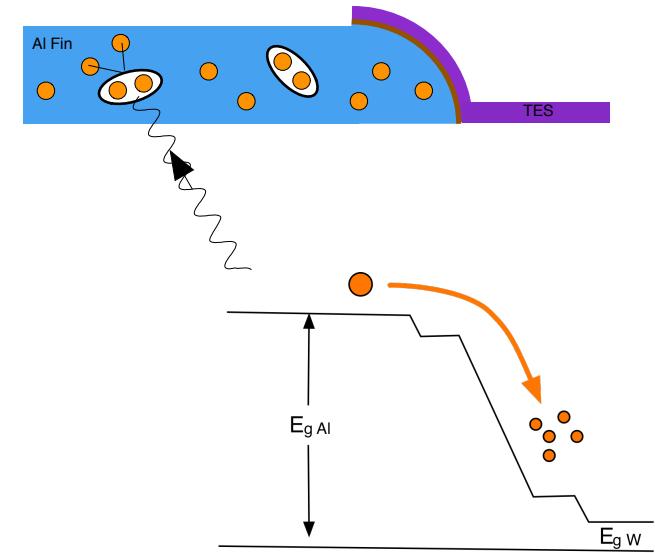
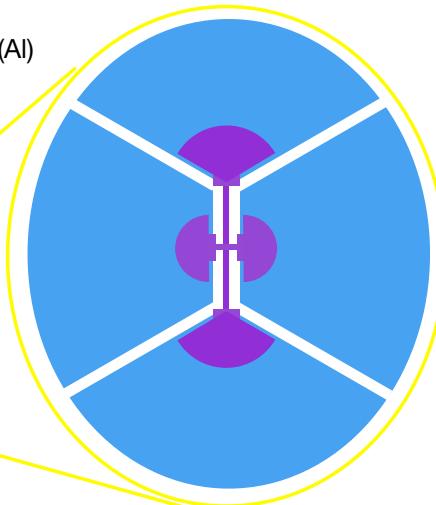
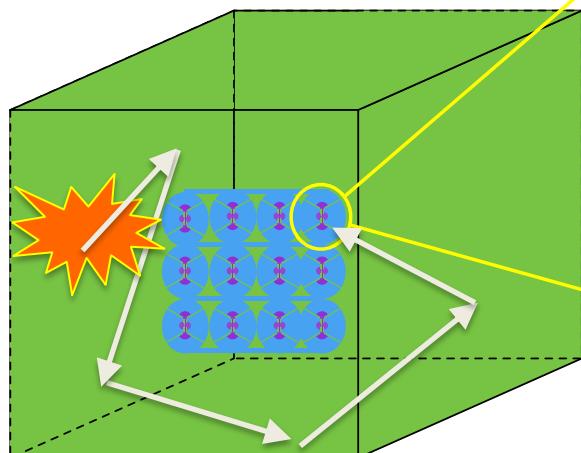
- Energy leaks out of the absorber through G_{ab} before its measured
- TES sensitive to power fluctuations through G_{tb}
- EDELWEISS has done this successfully

Athermal Phonon Sensor Technology

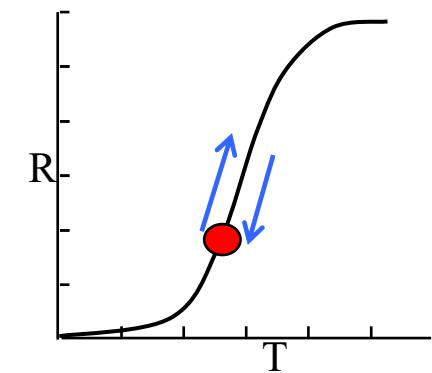
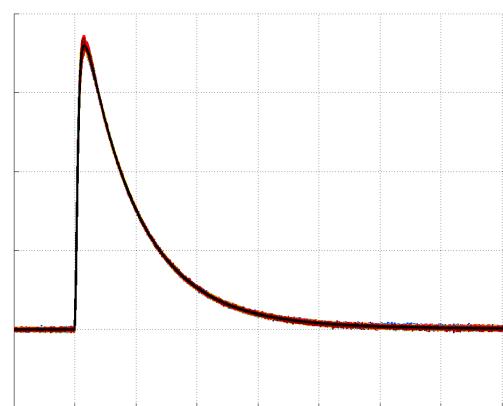
■ TES and QP collection antennas (W)

■ Athermal Phonon Collection Fins (Al)

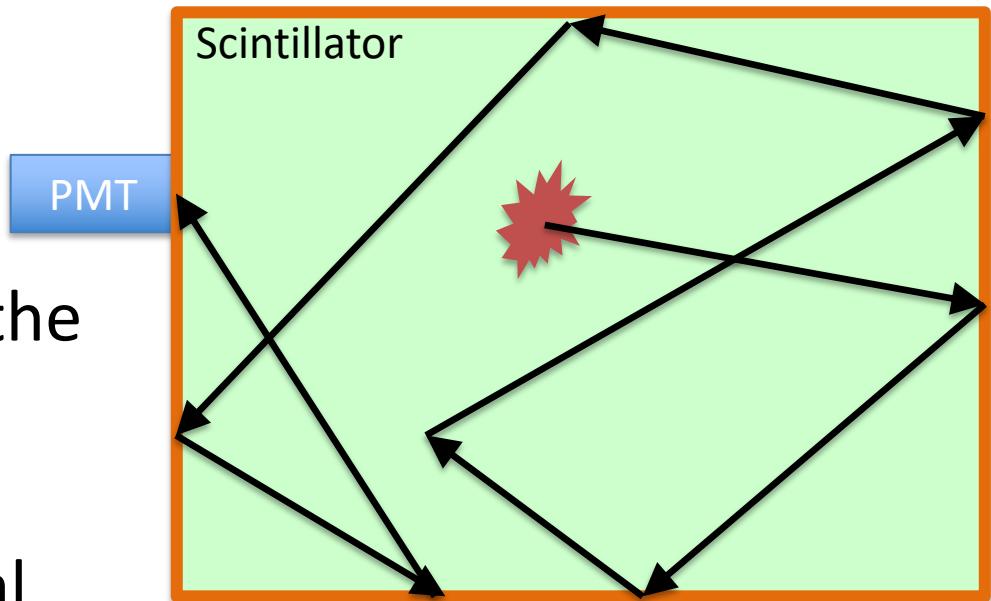
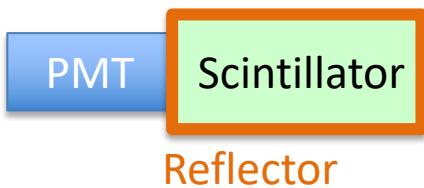
■ 1cm³ Polar Crystal



Collect and Concentrate
Athermal Phonons (>4K) into
Sensor before they thermalize



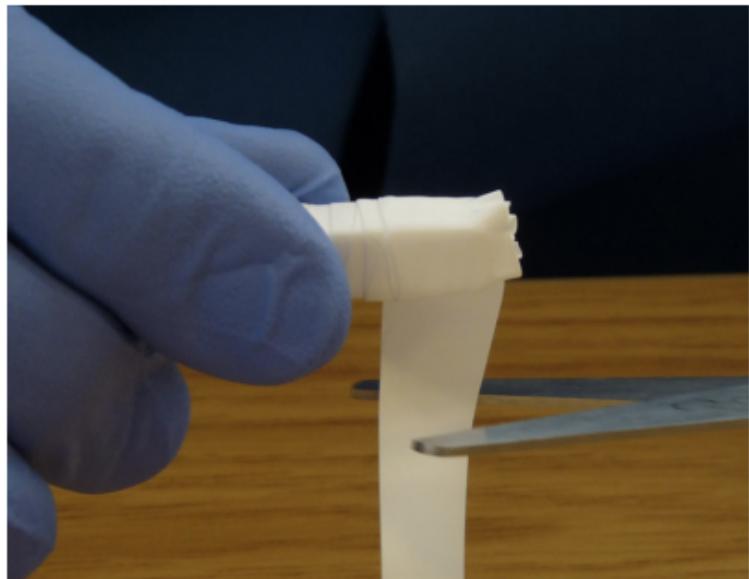
Excitation Detectors & Volume Scaling



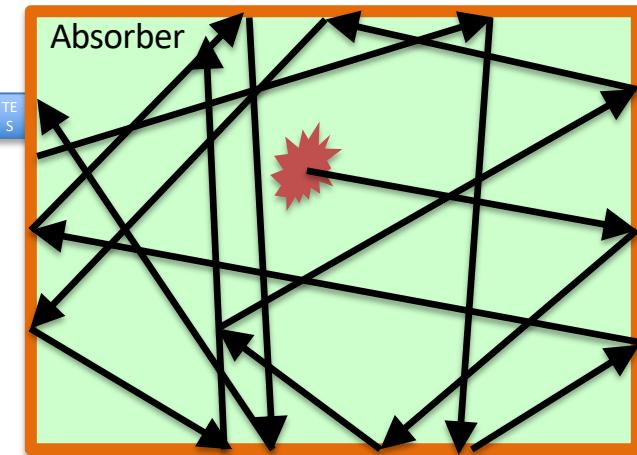
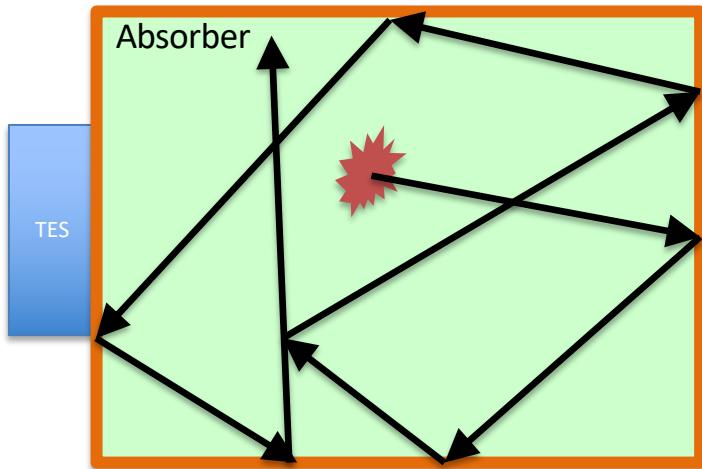
Will these detectors have the same energy sensitivity?

Yes, if:

- Lifetime of the athermal excitation (photon) is really long
- Excitation absorption dominated by sensor
- ~~Position Sensitivity~~

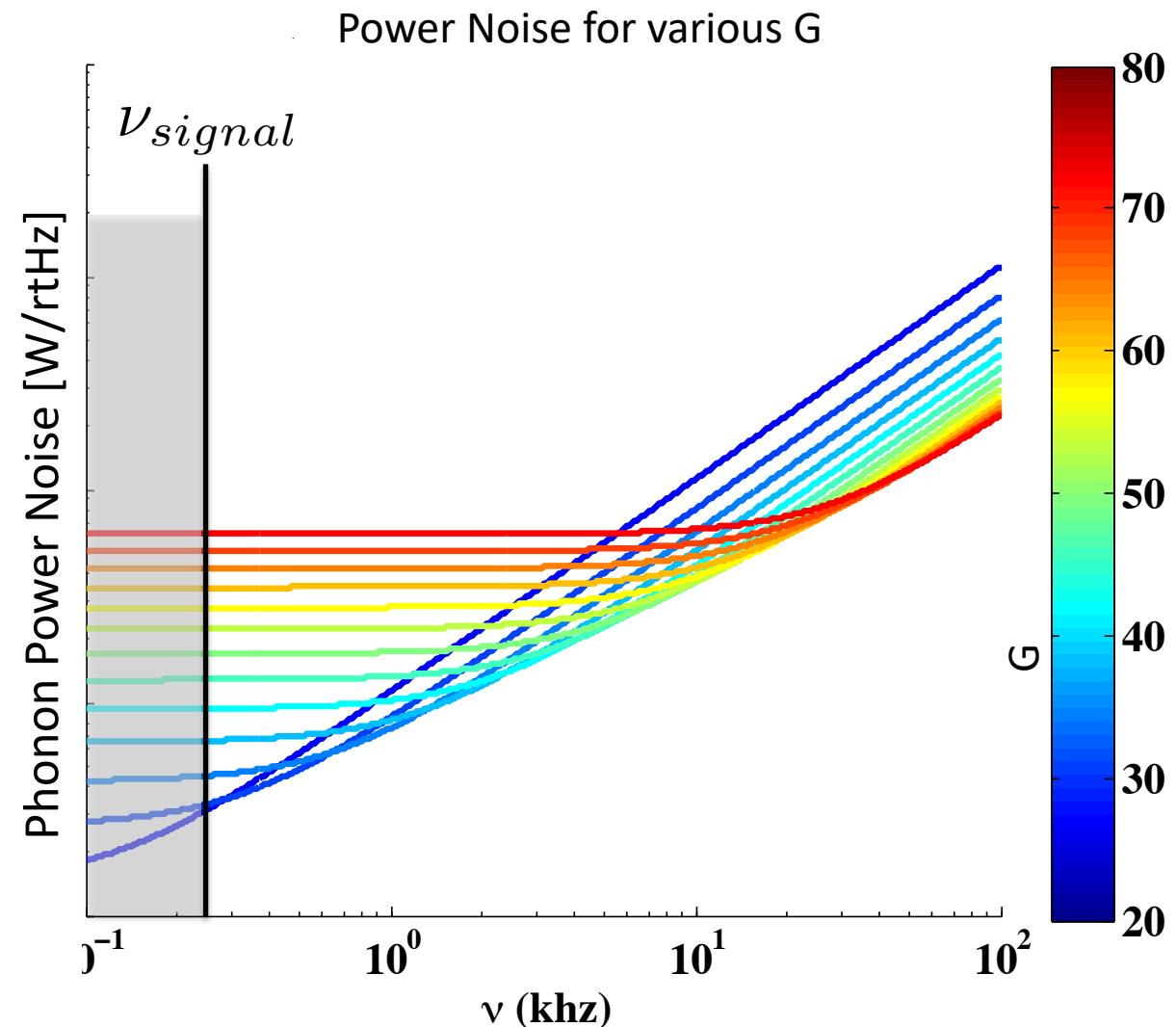


Optimizing the Athermal Phonon Excitation Detectors



Minimize the number/volume of the TES sensors instrumented on the surface to the point that you begin to see the bare surface thermalization rate

Athermal Phonon Sensor Sensitivity Scaling



$$G \propto T_c^4$$
$$S_{ptfn} = 4k_b T_c^2 G$$
$$\propto T_c^6$$
$$\sigma_E \propto T_c^3$$

- Lower ν_{sensor} (lower T_c) if $\nu_{\text{signal}} < \nu_{\text{sensor}}$
- Lower ν_{signal} (decrease Al coverage) if $\nu_{\text{signal}} > \nu_{\text{sensor}}$

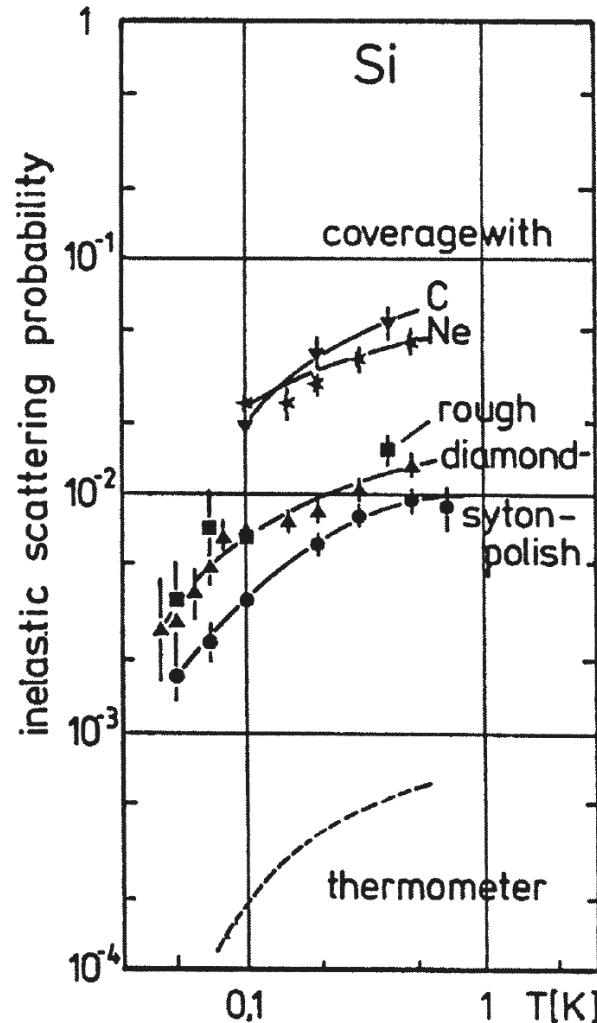
You can always say on VT_c^3 scaling (in principle)
45mK-> 10mK: 2eV -> 20meV

Athermal Phonon Thermalization at Surfaces

- Athermal phonon surface thermalization probability found to depend upon
 - Crystal
 - Surface roughness
 - Surface cleanliness

(W. Knaak et al, Phonon Scattering in Condensed Matter V, 1986)

- 0.1%-1% of the crystal surface covered with athermal phonon sensors ... 1/1000-1/100 thermalization probability needed
- Si, Ge -> ok



Large Area Photon Detectors

Large Area Photon Detector



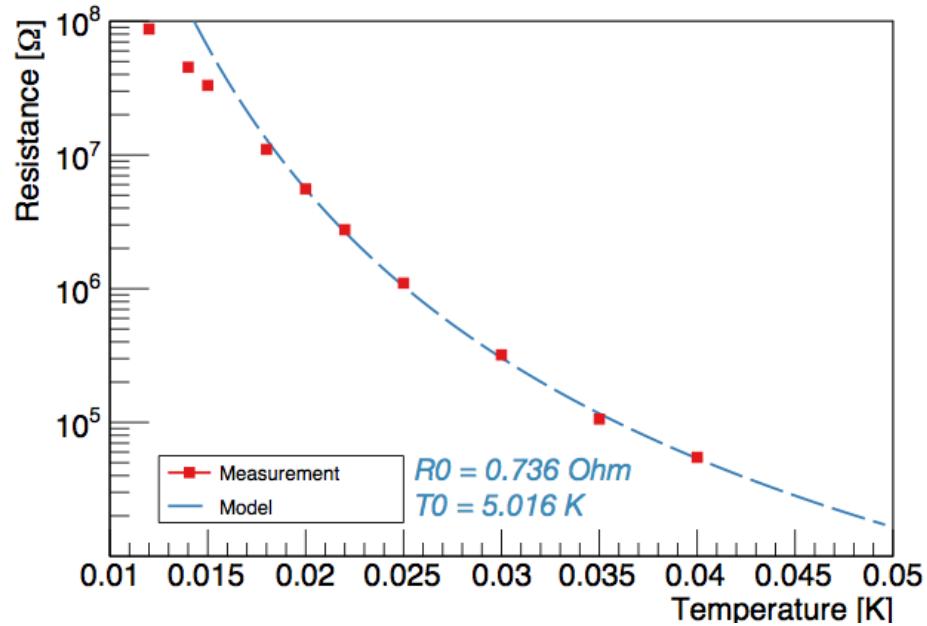
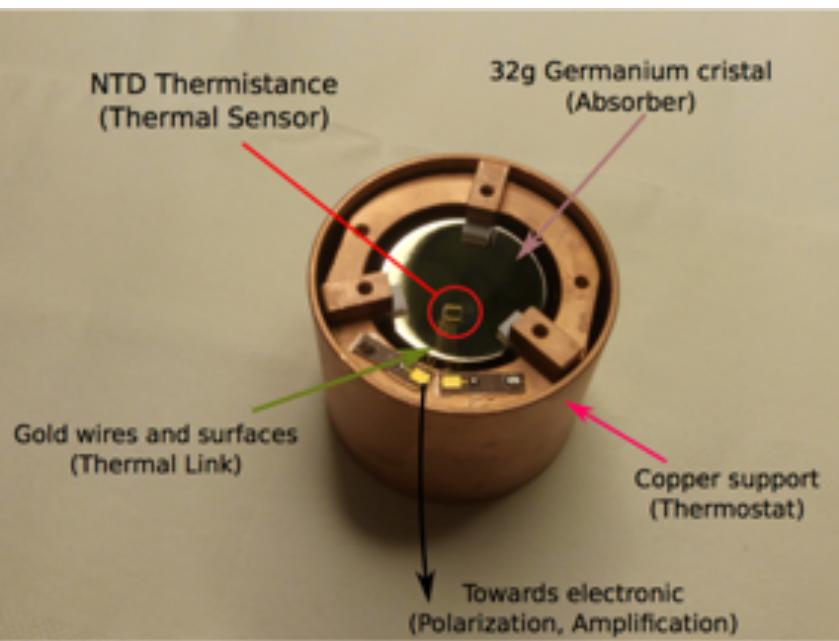
CRESST 2 Light Detector



	Sensor	Area (cm ²)	σ [eV]	σ/\sqrt{A} [eV]
CRESST 2 LD Rothe et al JLTP 193,1160 (2018)	W TES	12.5	4-7	1.1-2.0
LAPD (CDMS tech)	W TES	45	3.9	0.58

NTD
[Neutron Transmutation Doped Ge
Thermistor]

NTD

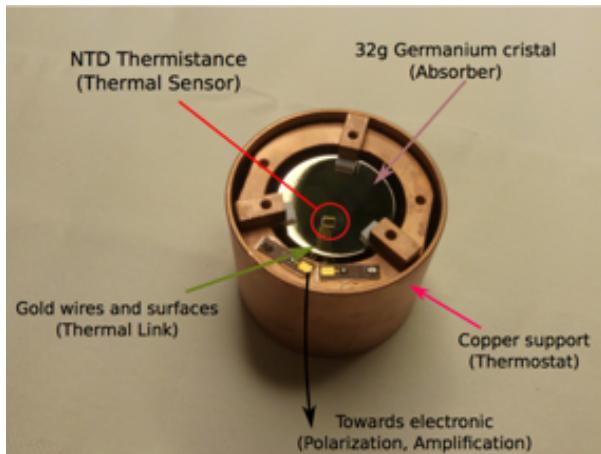


Thermal Calorimeter: $\sigma^2 \propto VT^3$

- Provided limited by TFN noise

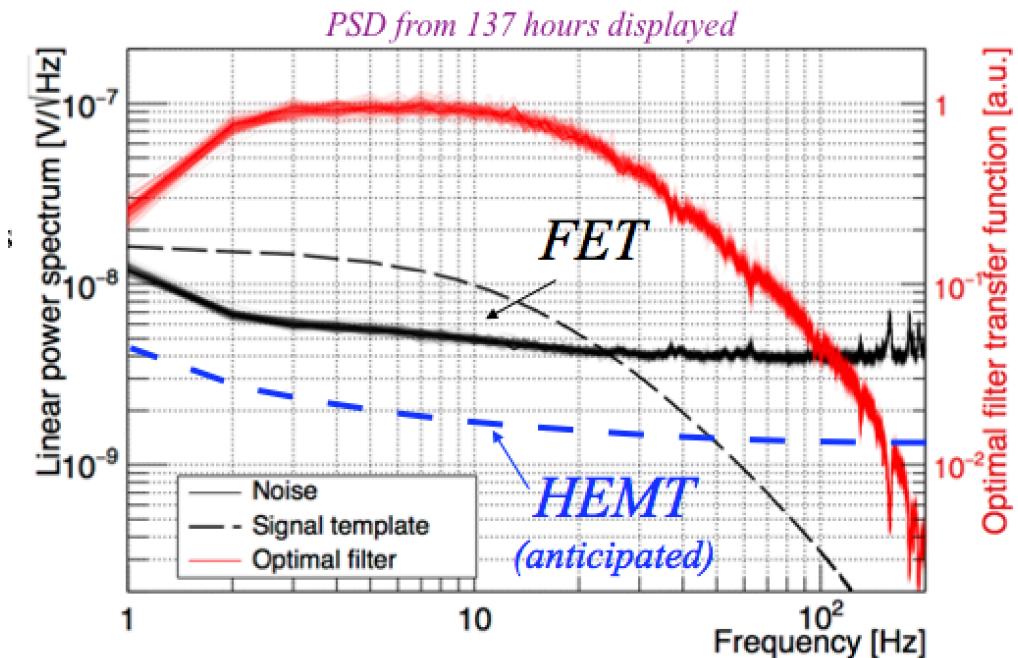
Thermal/Athermal Phonon Detector

Ge Athermal/Phonon Detector



- 17.7eV on 33.4g Ge detector
 - 50eV on 200g Ge detector
- (x8 better than EDELWEISS 3 800g)

Hope to get to 10eV with improved electronics



Large Area Photon Detectors

Large Area Photon Detector



CRESST 2 Light Detector



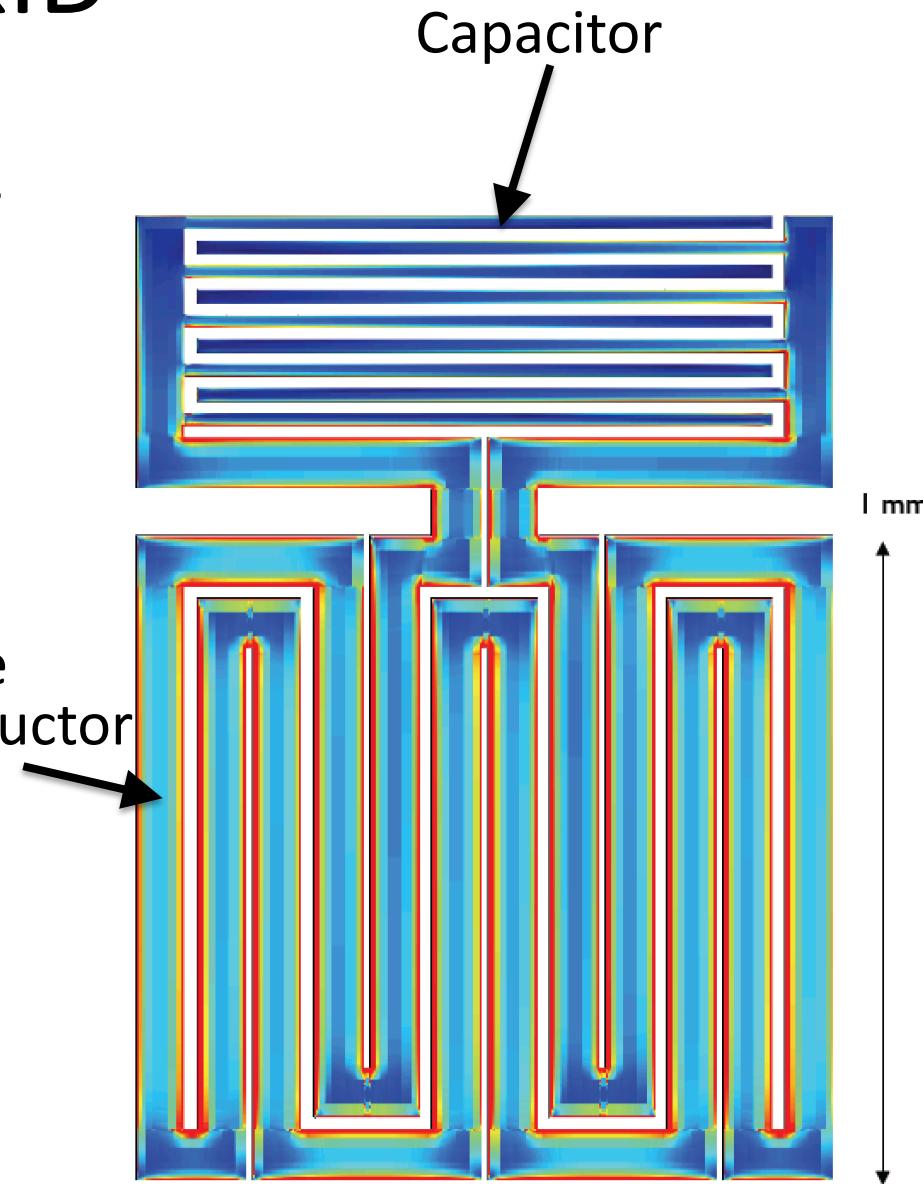
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LMO-3 LD E. Armengaud et al, Eur. Phys. J. C (2017) 77 :785	NTD	5	7.7	3.4

MKID

MKID

Superconductors have an AC inductance due to inertia of cooper pairs

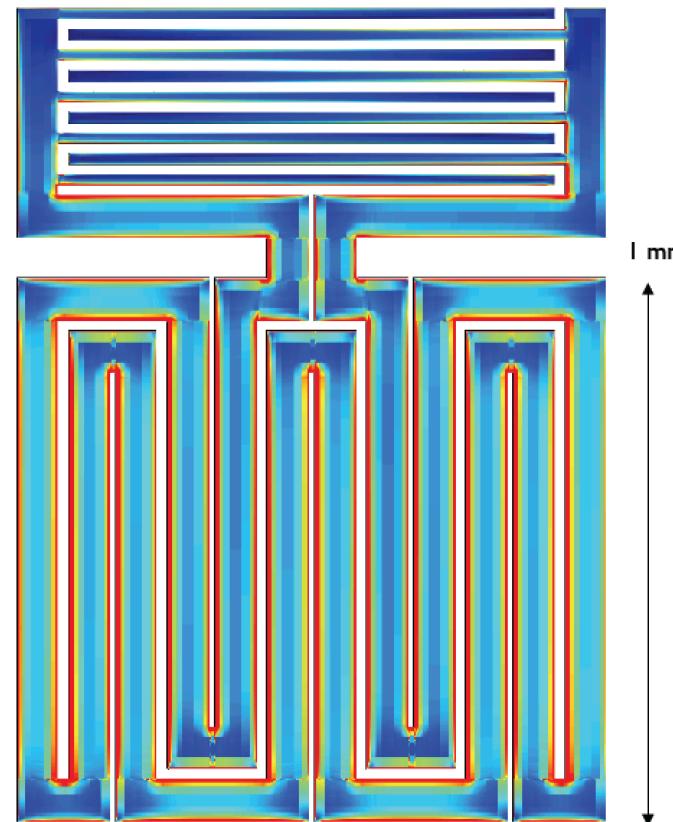
- fewer cooper pairs -> more inductance -> lower resonant frequency
- Easily Multiplexed
- 1mmx1mmx40nm active volume
- Frequency tuned by changing inductor length
- Capacitor: standard interdigitated capacitor to minimize TLS noise ... can be made out of Nb to avoid phonon absorption



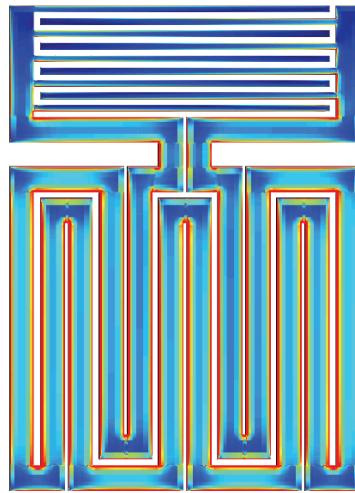
MKID Sensitivity

$$\sigma_E = 2\Delta \sqrt{\frac{\eta_a}{\chi_c \chi_{qp}}} \sqrt{\frac{k T_a N_0 V_r}{\left[2N_0 \Delta \frac{\partial(\sigma_1 / |\sigma(0)|)}{\partial n_{qp}} \right] Q_s}}$$

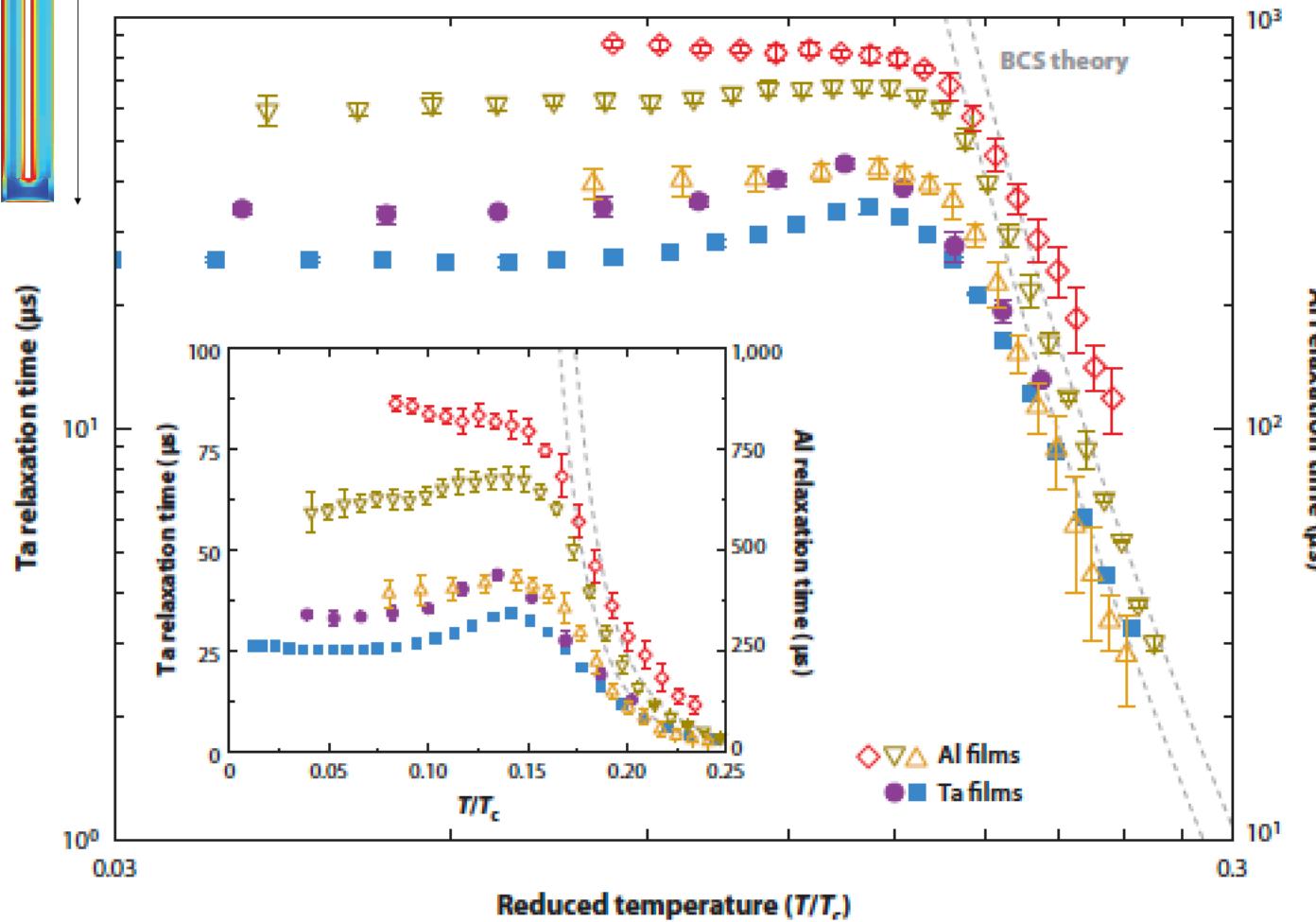
- Scales with sensor volume
- Scales with amplifier noise temperature
 - 4K \rightarrow 70mK with parametric amplifier
- Scales with T_c / Δ
- Assumes no excess quasi-particle density
- Not sensitive to all frequencies of EMI



Excess Quasi-particle Density

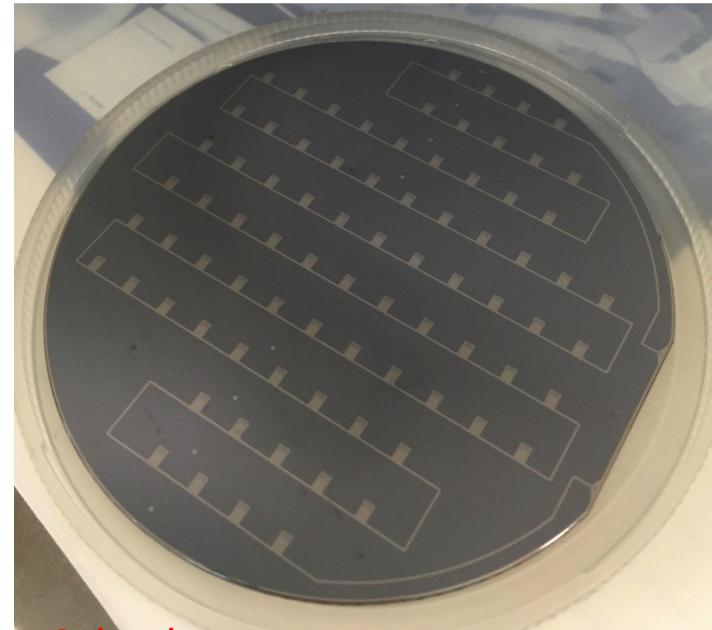
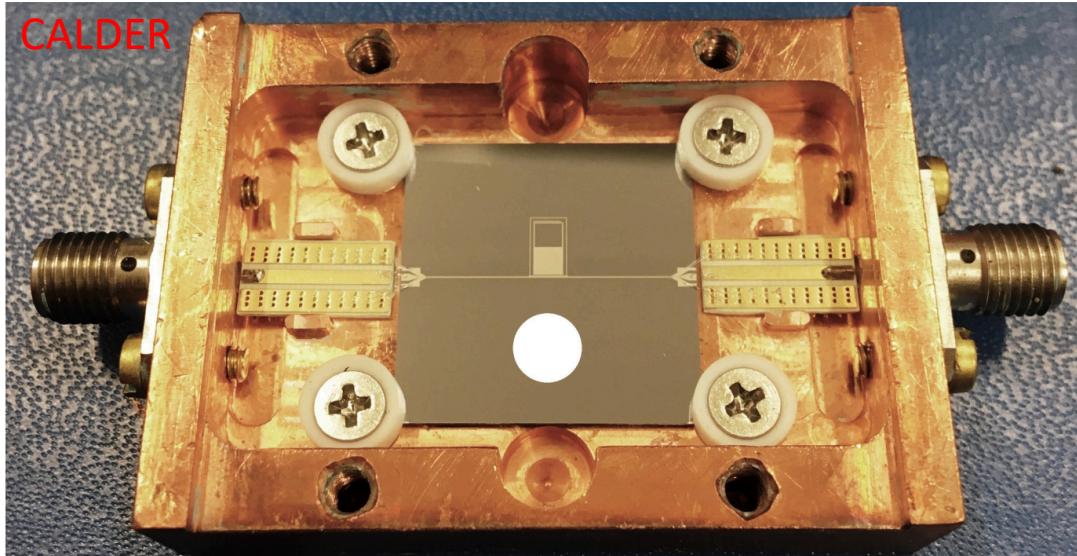


asymptotic regime; limiting excess qp density n_* , or something else?
related to disorder? (Barends et al implantation experiment)



Barends et al PRL (2008)
as reproduced in Zmuidzinas, ARCMP (2012)

MKID: Athermal Phonon Sensor



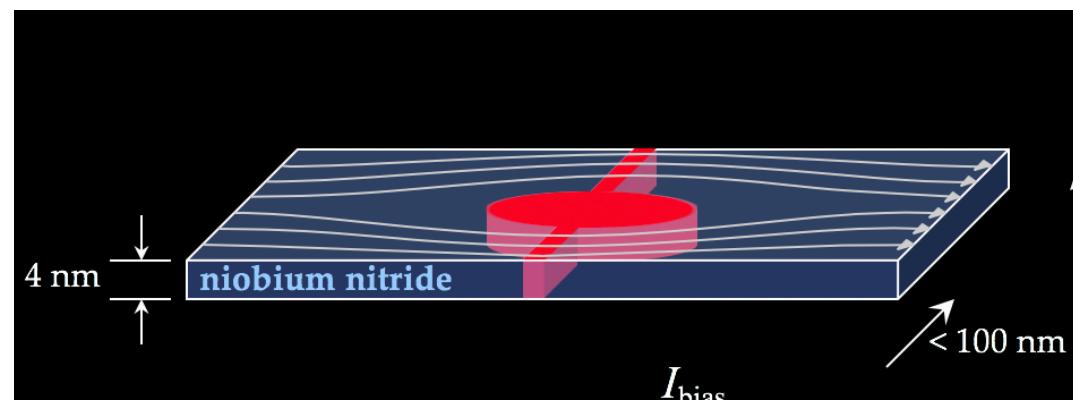
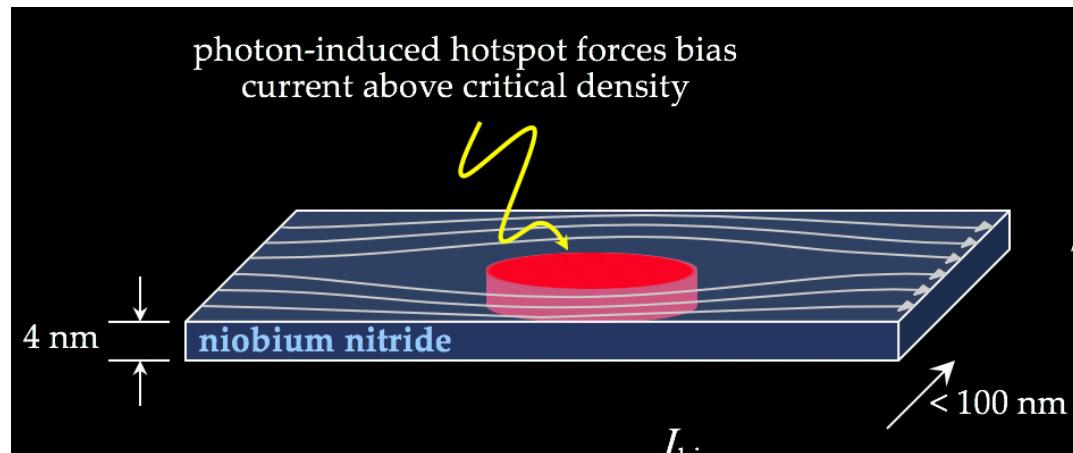
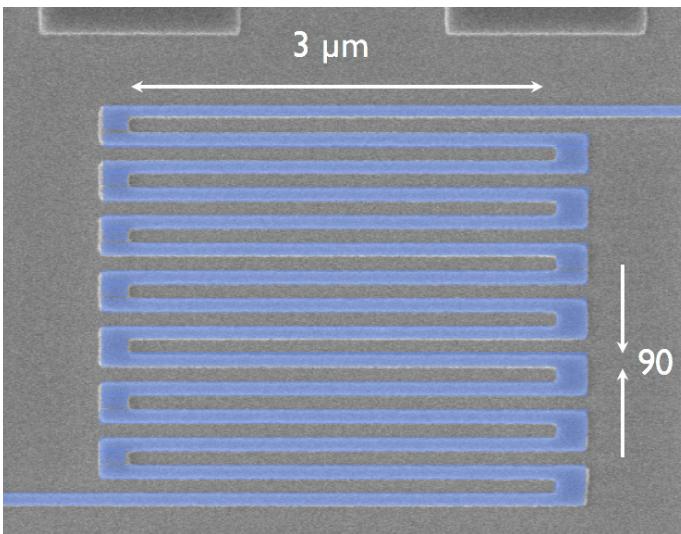
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LMO-3 LD E. Armengaud et al, Eur. Phys. J. C (2017) 77 :785	NTD	5	7.7	3.4
CALDER 1801.08403	Al/Ti/Al MKID	4	26	13

MKID R&D:

- Better Amplifiers (parametric amplifier at 70mK)
- Excess Quasi-particle density
- Two Level Systems

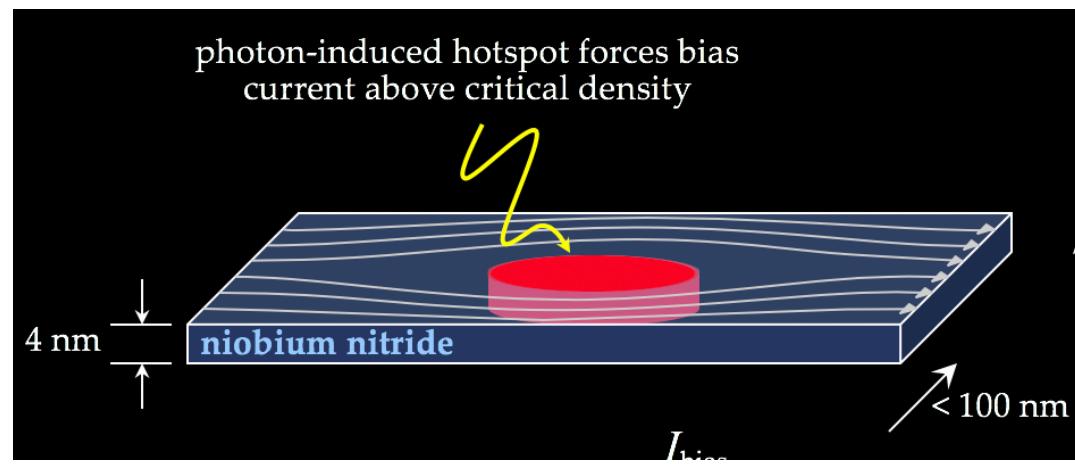
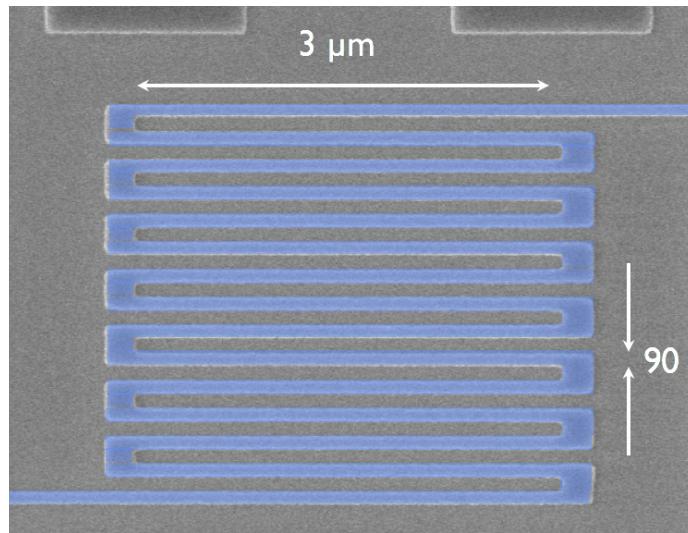
SNSPD
Superconducting Nanowire Single
Photon Detector

SNSPD: Operating principle



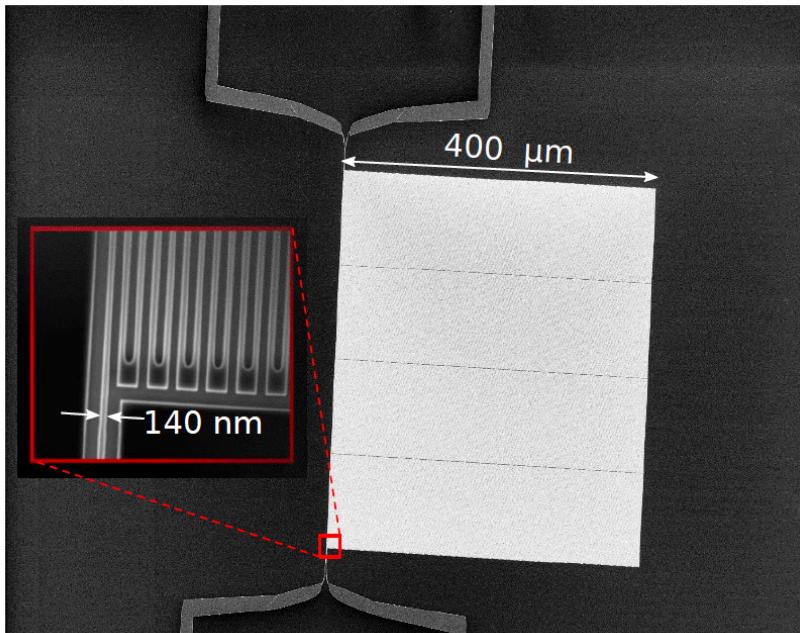
- SC wire biased very near critical current. Event causes nanowire to switch to normal state
- Natural Energy Amplification
- Event Measurement ... doesn't measure energy

SNSPD: Energy Threshold Scalings



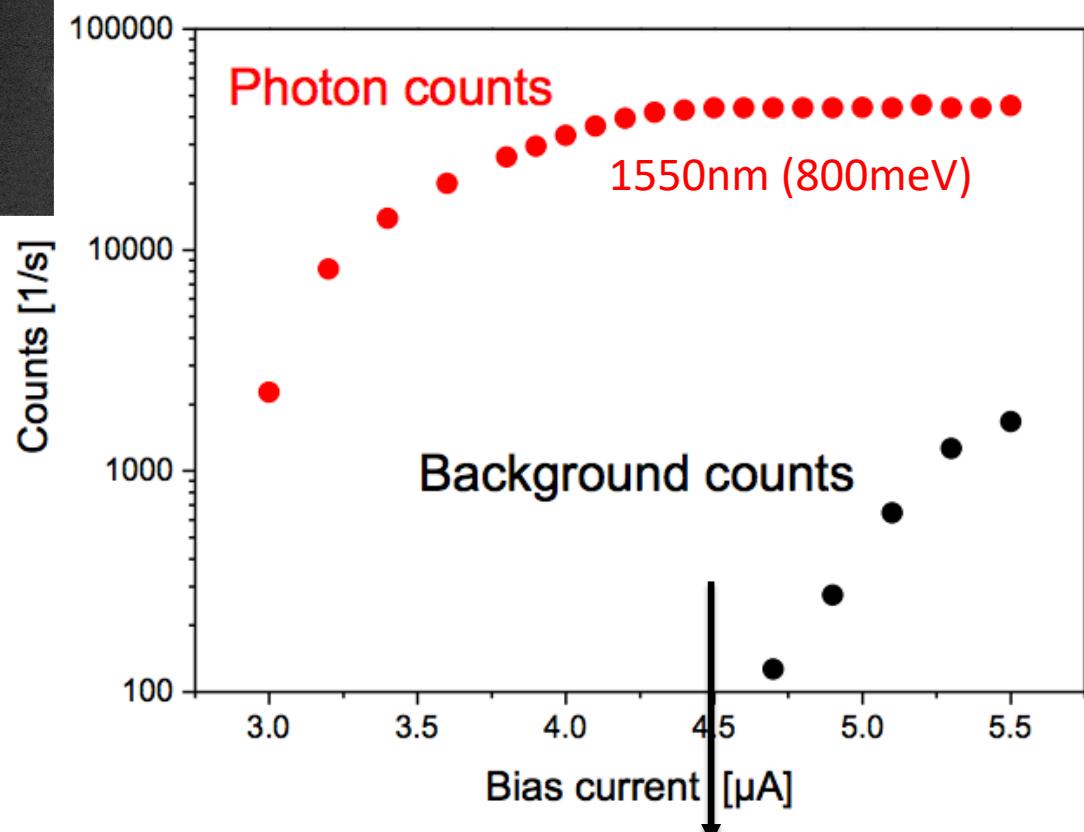
**Scales with cross sectional area, not volume.
Can make the meander as long as you want**

Current Performance

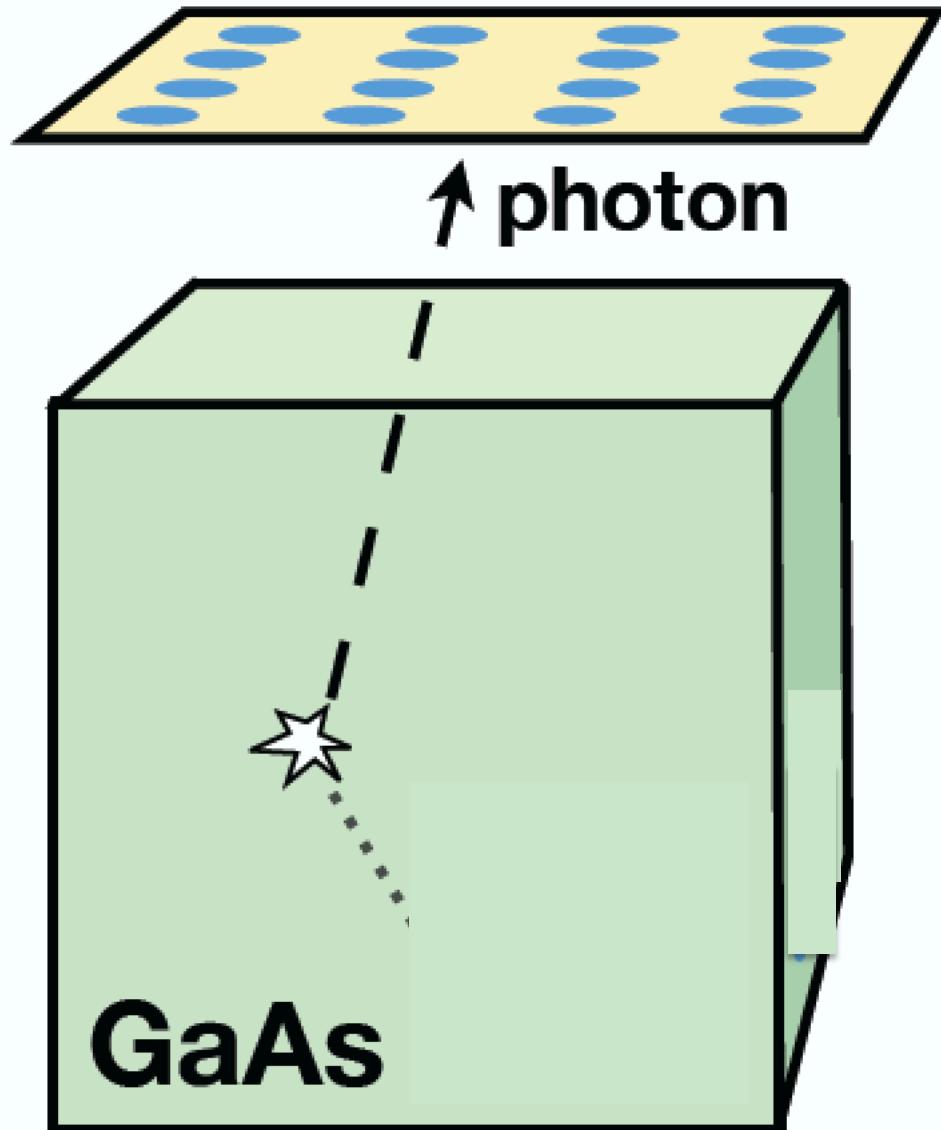


- 1903.05101
- WSi 400umx400umx7nm Meander

< 10^{-4} Hz dark count rate
@ 4.5 μ A



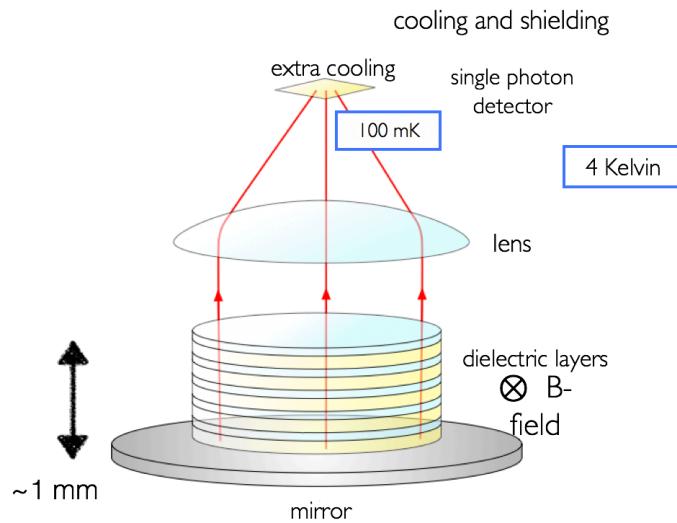
Measuring Energy With Multipixel SNSPD Arrays



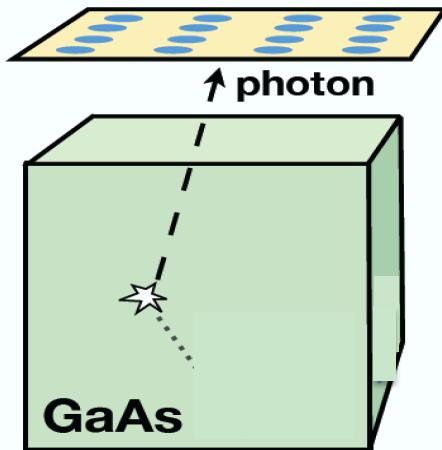
In the limit of large pixel number,
the probability of 2 photons
hitting the same pixel is
small (and can be corrected)
... it's the same probability
distribution as the shared
birthday problem

SNSPD Applications

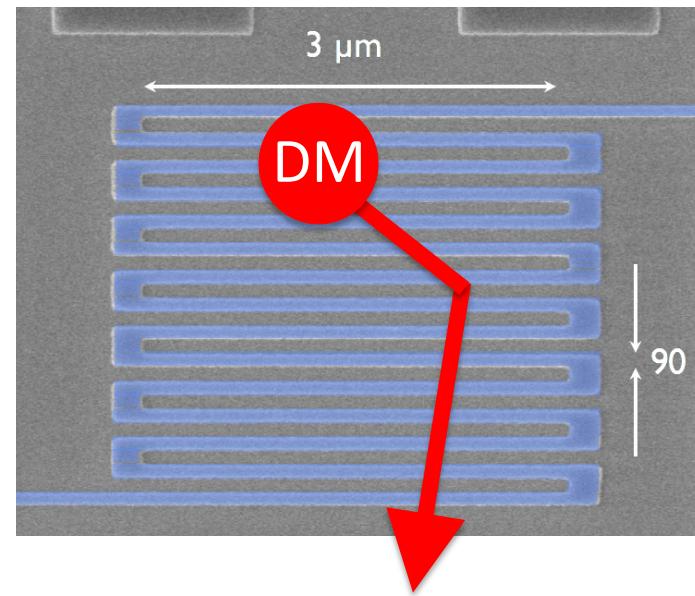
Optical/IR Haloscopes



Inelastic Electronic Recoil DM Search with Scintillator



Bulk DM search

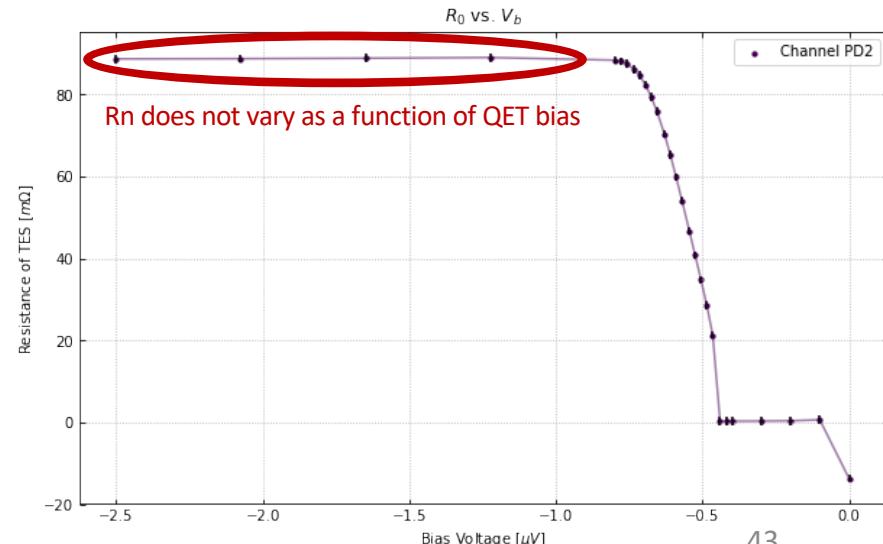
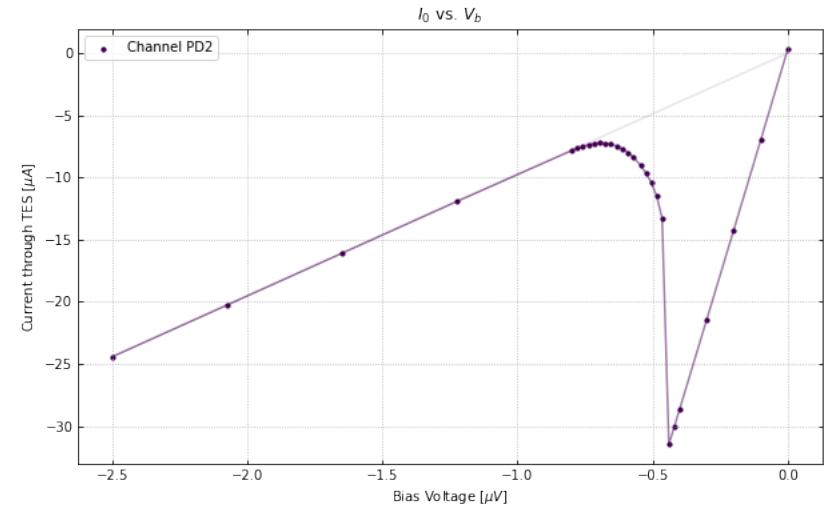
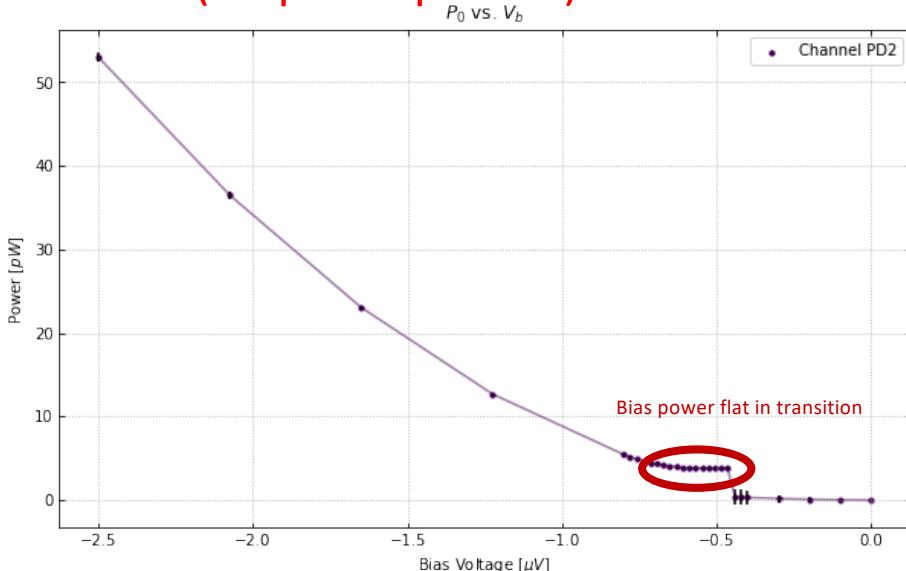


- 1903.05101
- 4.3ng per pixel
- 2.3×10^8 channels for 1g

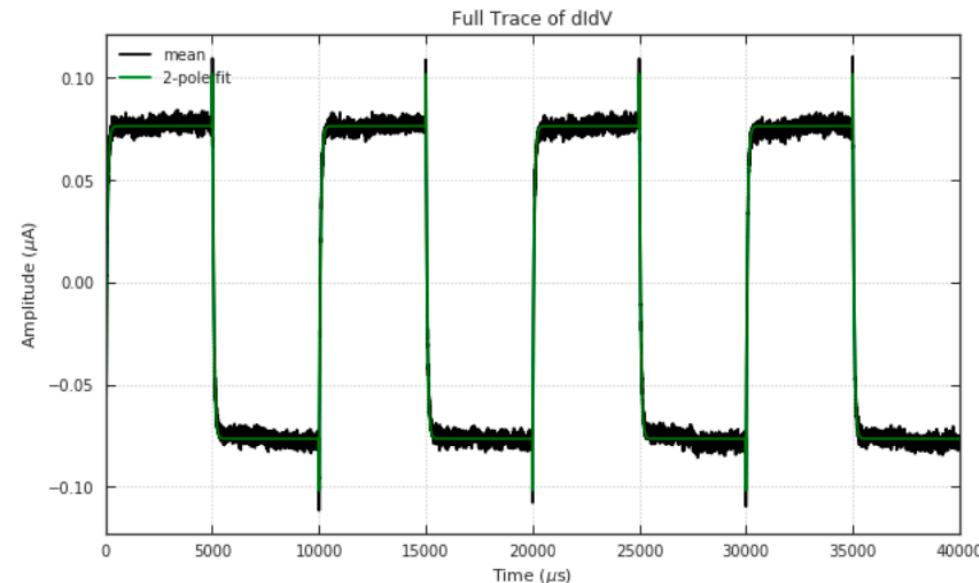
Backup

Measured Performance: Tc & IV

- $T_c = 41.5\text{mK}$
- IV curves show that the detector and electronics are behaving well
 - $R_n = 88 \text{ mOhms}$ (**300mOhm Expected ... TES too wide!**)
 - $R_p = 8 \text{ mOhms}$
 - Bias Power (P_0) = 3.9 pW
(1.4pW expected)

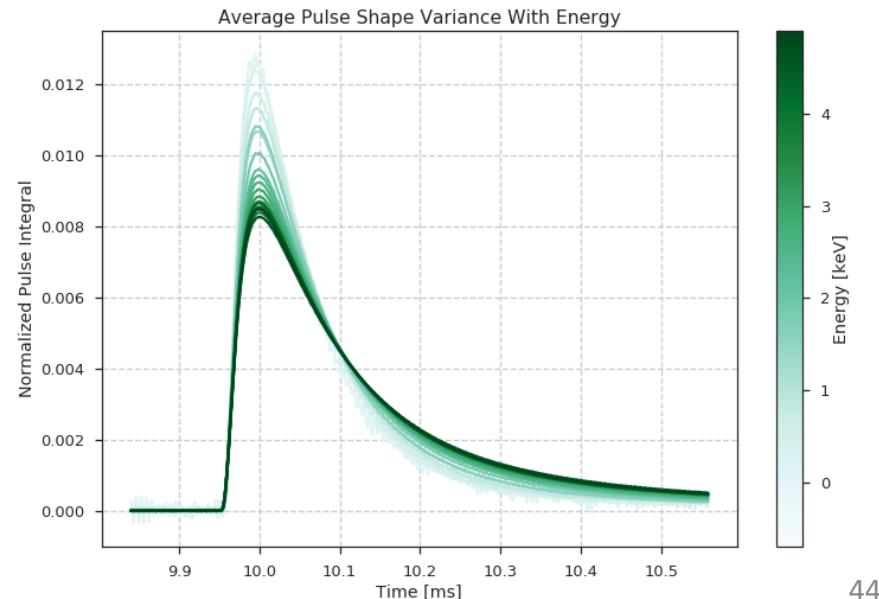


Measured Performance: dI/dV



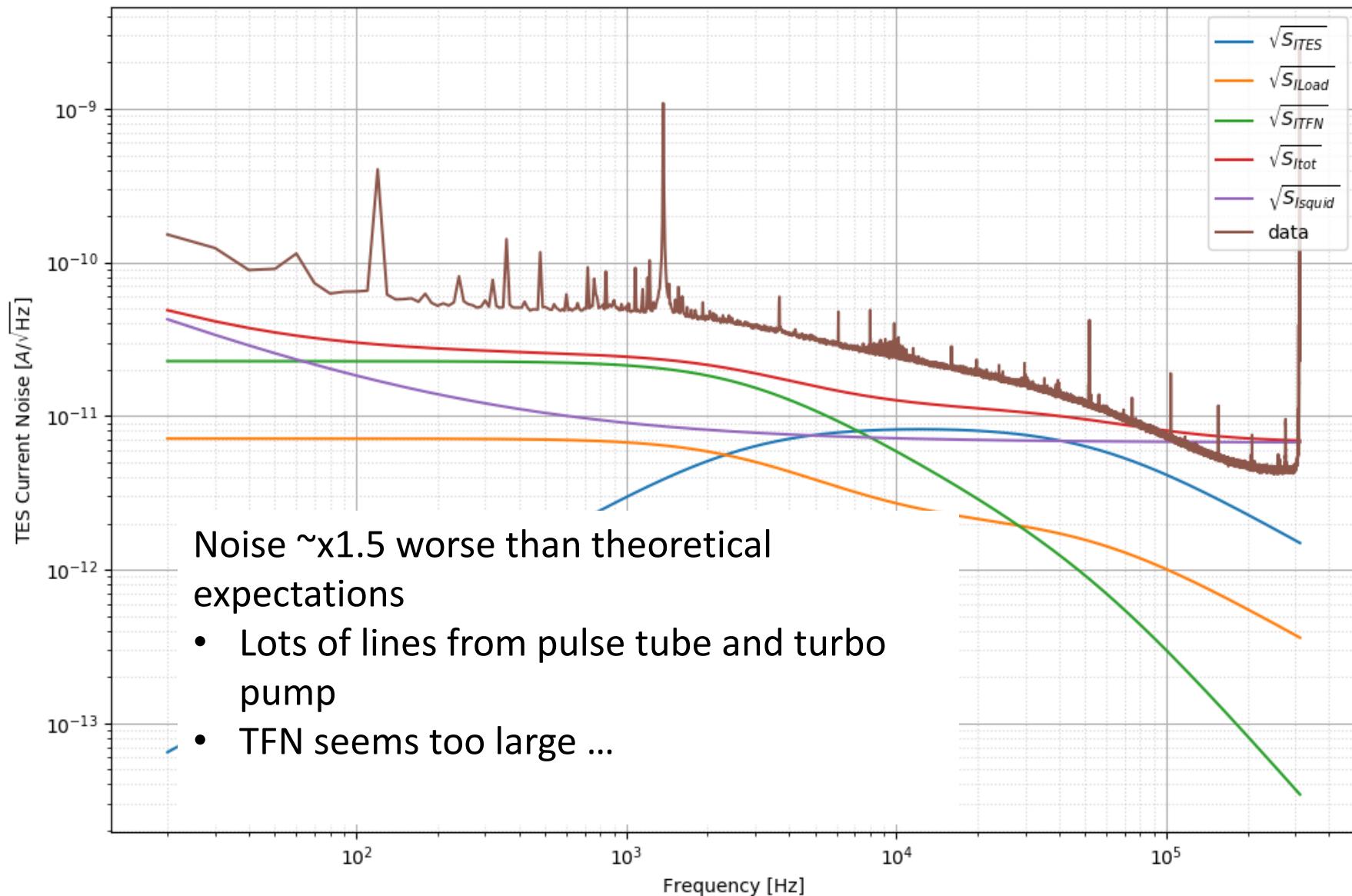
- Therefore, we expect phonon signals to have a 20us rise time (athermal phonon collection) and a 60us fall time. **Seen for low energy comptons in average pulse shape!**
- Pulse shape varies with energy due to local TES saturation.

- TES sensor pretty fast @ 60us. However, it's not as fast as the estimated athermal phonon collection (20us)



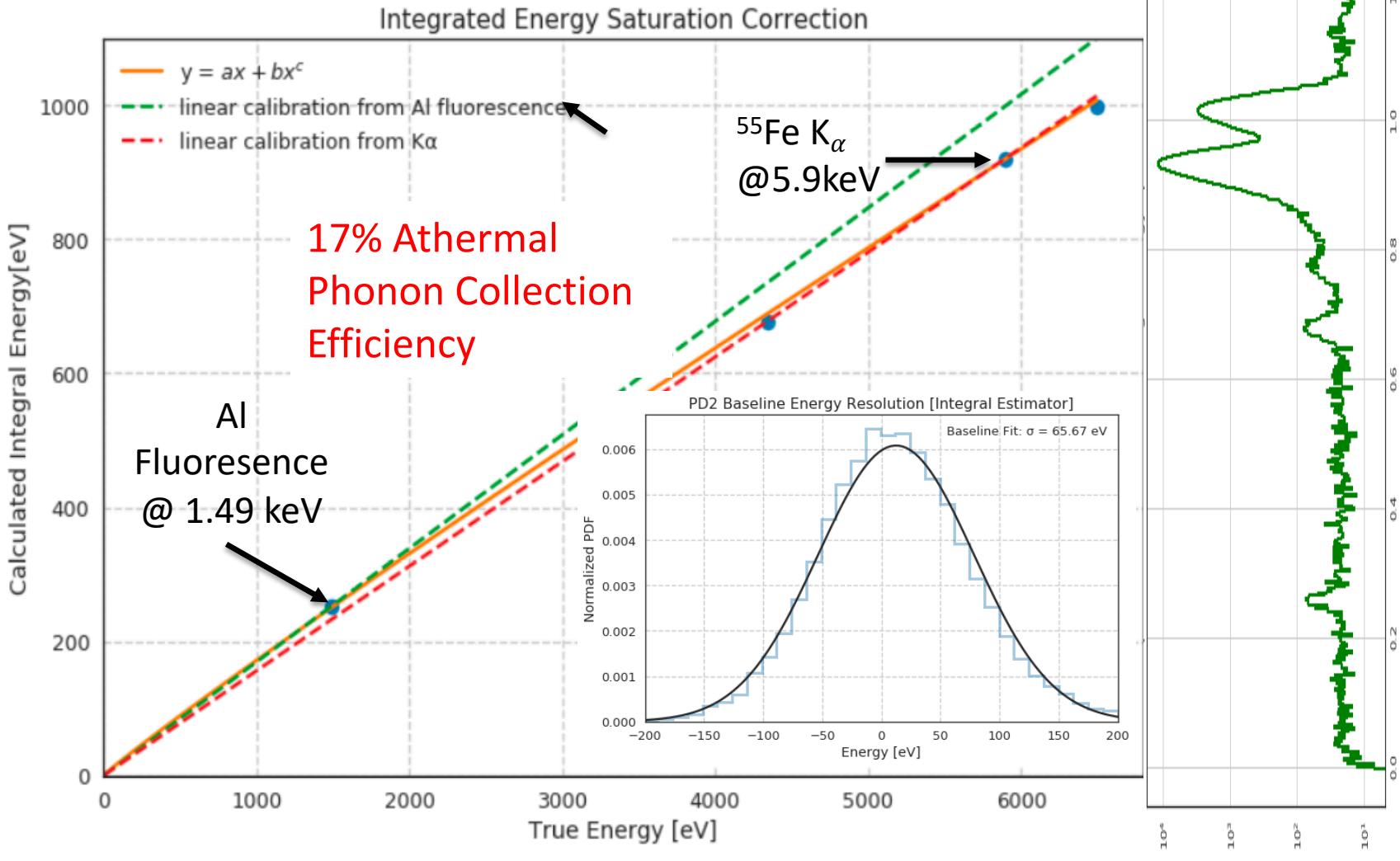
Measured/Theoretical Noise

Current Noise For $R_0 : 32.00 \text{ m}\Omega$

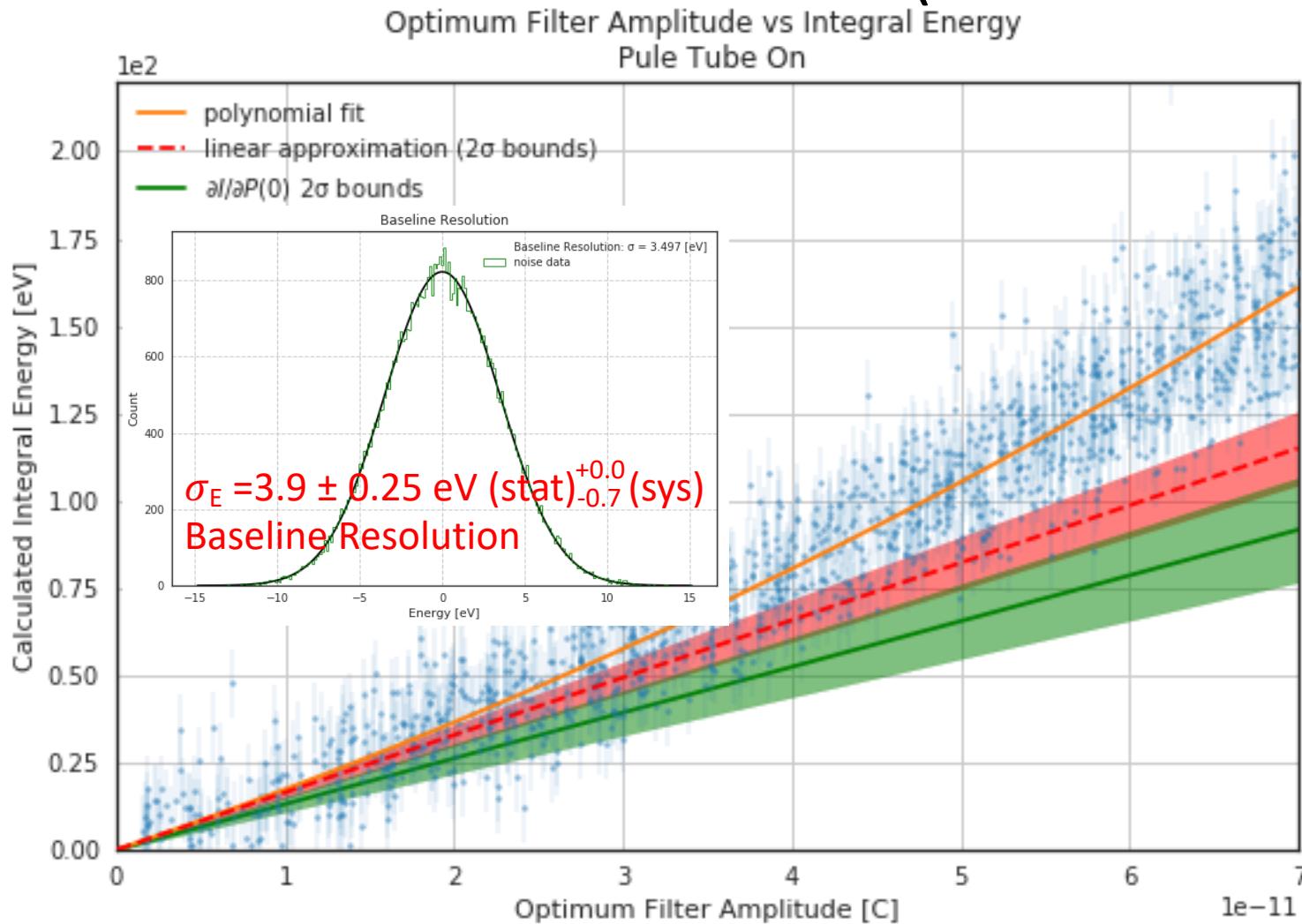


Integral Estimators for relative ^{55}Fe calibration

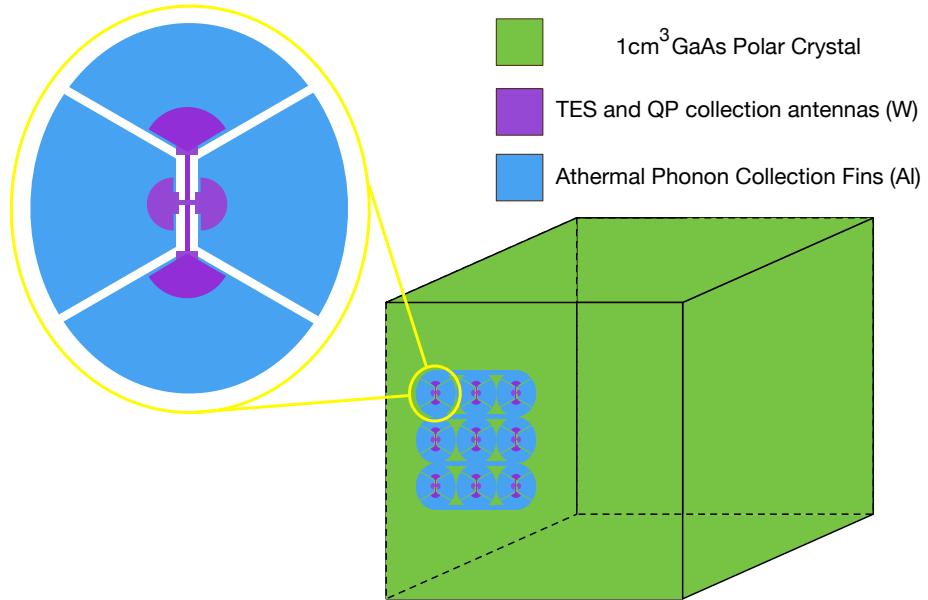
- Since pulse shape has significant variation with energy, we must use noisy but minimally biased DC estimators to fit the ^{55}Fe calibration lines



Calibrating Pulse Shape Dependent Energy Estimators to the DC estimator (Pulse Tube On)



Surface Dark Matter Search Completed at SLAC



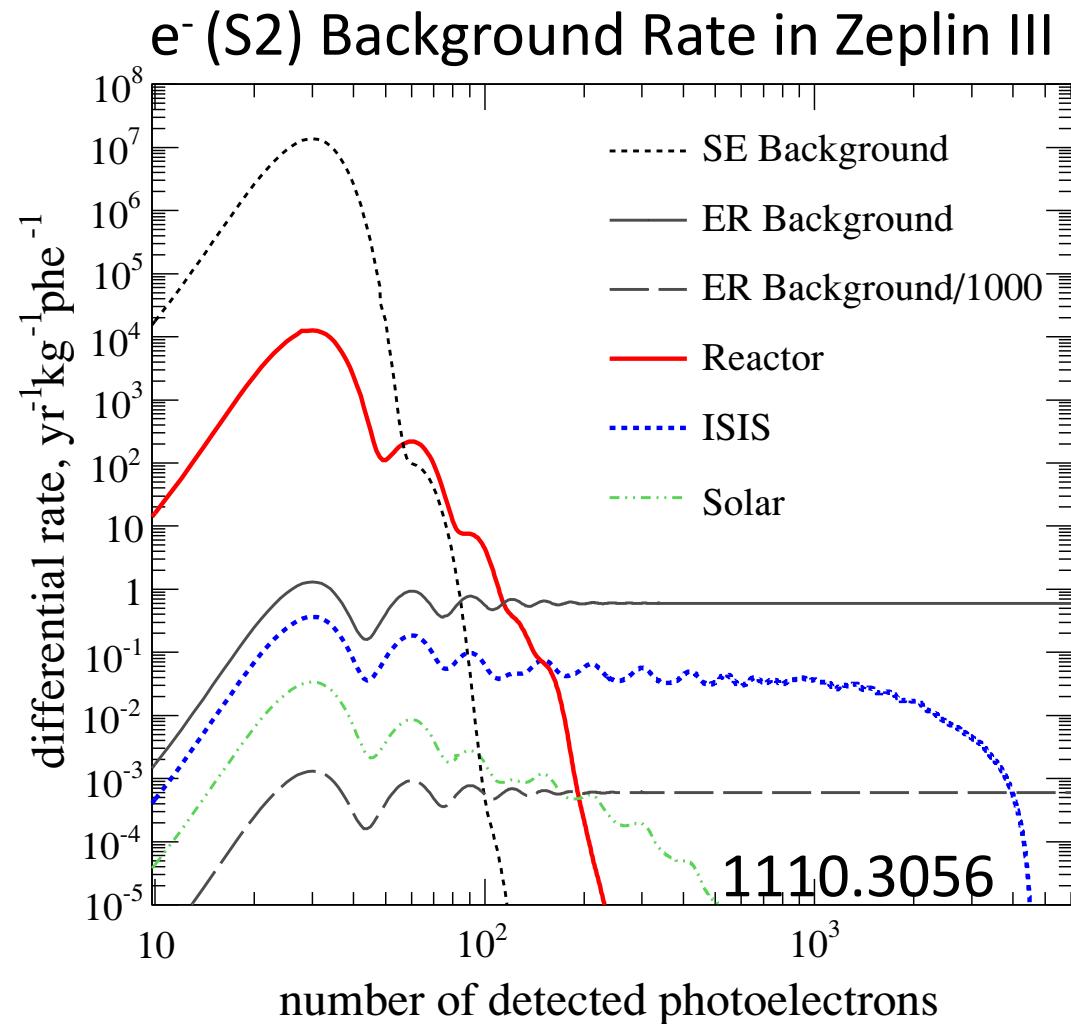
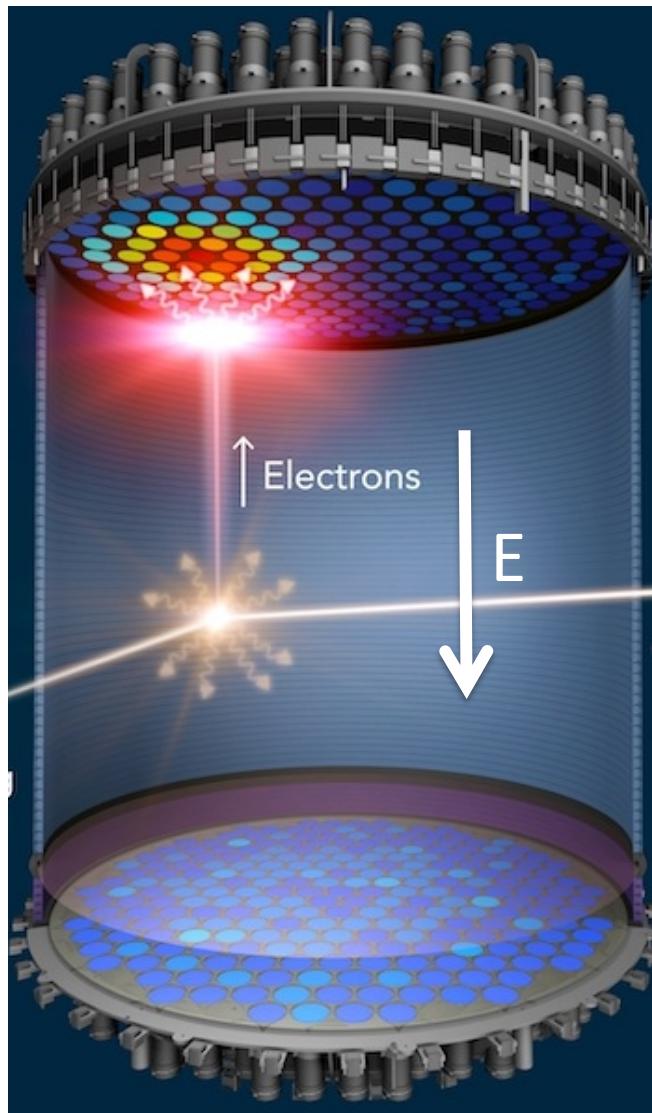
Prototype Design Estimated Sensitivities

New 1cm³ Prototype Test Design

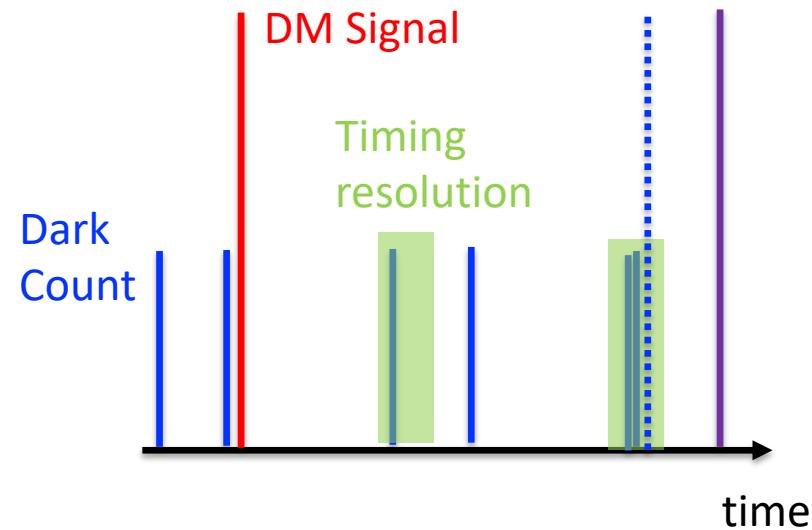
# TES	100
TES Dimensions	50um x 2um x40 nm
TES R _n	320mOhm
Fin Length	125um
W/Al Overlap	15um
Fractional Al Coverage	1%
T _c	40mK
Bias Power	48fW
Power Noise	5.1e-19 W/rtHz
Phonon absorption time	106us
Sensor fall time	97us
Collection efficiency	19%
σ_E	219 meV

- With a Si Absorber: single e/h sensitivity without Luke-Neganov gain. Can be used for inelastic electronic recoil DM
- World Leading Elastic Nuclear Recoil DM search potential

Problem: Detector Backgrounds in TPCs



Dark Leakage Needs to be Poissonian



$N e^-$ background

- $N 1e^-$ events occur within detector timing resolution (Poissonian Leakage)
- $N e^-$ leakage event (Non-Poissonian Leakage)

Xenon TPCs:

- $R_{1e^-} = 10\text{Hz}$
- $\Delta t = 100\text{ns}$
- $R_{2e^-}(\text{Poissonian}) = 10^{-5}\text{Hz}$

Due to fast timing Xe TPCs can handle a relatively high $1e^-$ rate and still have $2e^-$ bin free. Unfortunately, leakage is non-poissonian (R&D needed)